

# Summary

*International Conference on the Advancement Silicon Photomultipliers*

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## SiPM Large Scale Characterization

Topical group  
Conveners:  
Herbert Orth,  
**Nikolay Anfimov**

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Schwetzingen, Germany June 2018

# Topical group's talks

- ❖ T2K
- ❖ DarkSide
- ❖ COMPASS ECAL0
- ❖ NICA-MPD ECAL
- ❖ ScTiL for PANDA
- ❖ Mu2e
- ❖ DANSS
- ❖ nEXO
- ❖ MEG-II
- ❖ AMADEUS
- ❖ CALICE
- ❖ CMS
- ❖ AD
- ❖ AStroparticle
- ❖ PET-Tomography

Section of KETEK SiPM Microcell

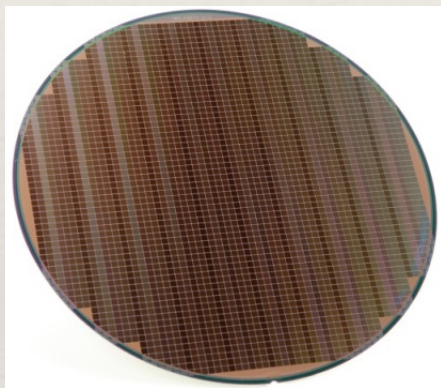
Bias Line

Quenching Resistor



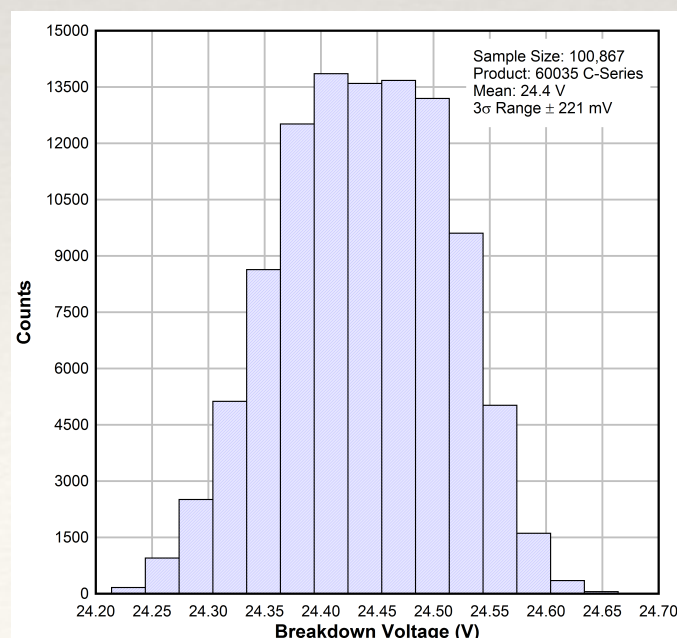
# Wafer tests (Broadcom, SensL)

**Broadcom company presented some wafer tests.  
But slides are not available**



Wafer test are very important to control production:

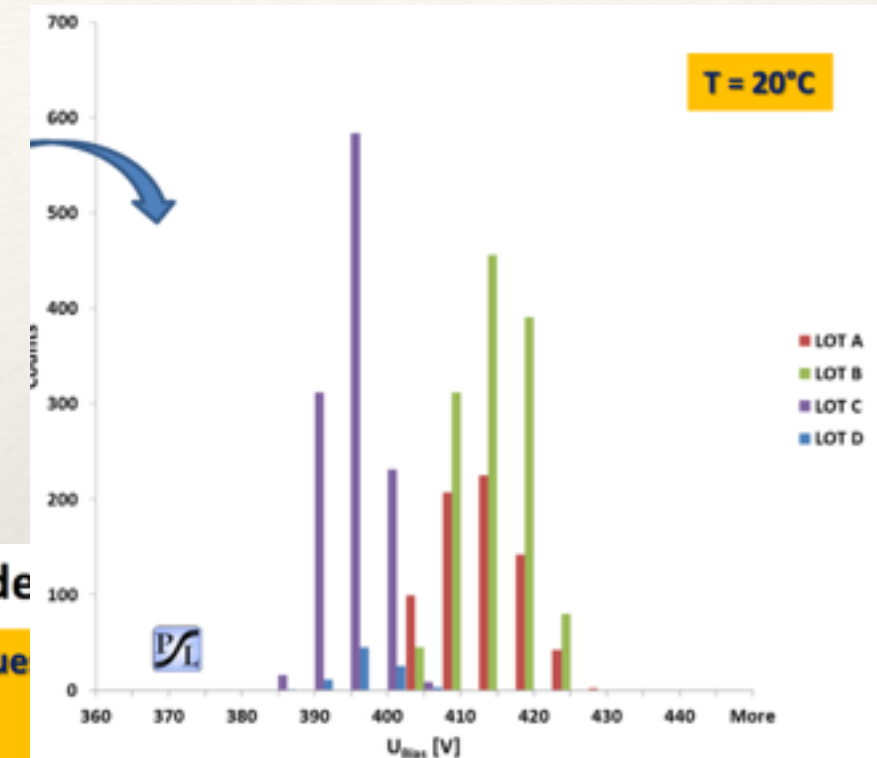
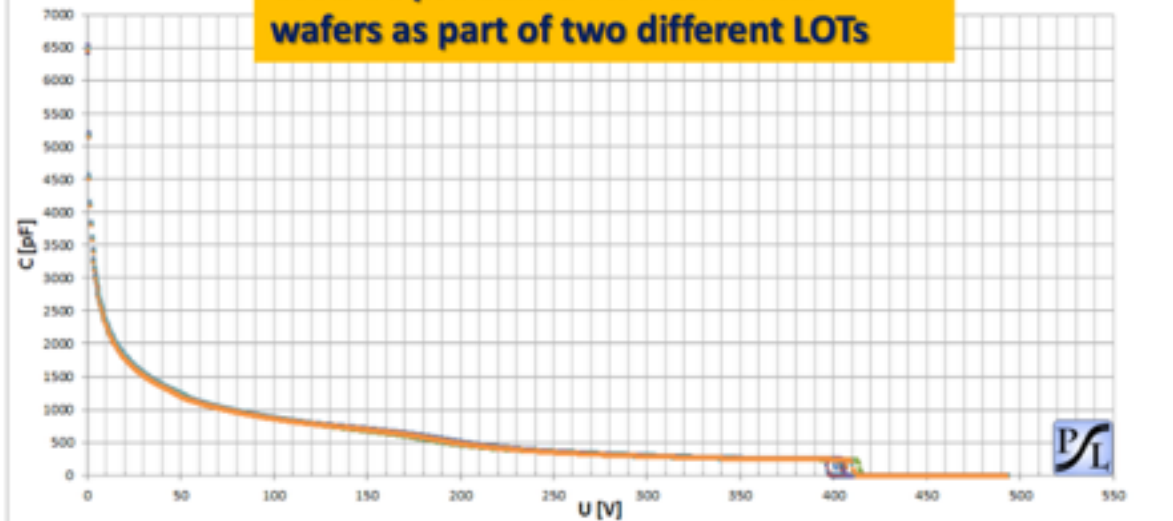
- Performance of SiPM @ wafer level -> feedback
- Uniformity and patterns give very important feedback
- Possibility to select dices (for arrays or other things)
- IV-curves (**LL-spectra as sampling tests?**)



# APD experience (A. Wilms)

APD is not SiPM  
but some testing methods are close to SiPM

example of 12 C-V characteristic curves  
of APDs produced on 8 different  
wafers as part of two different LOTs

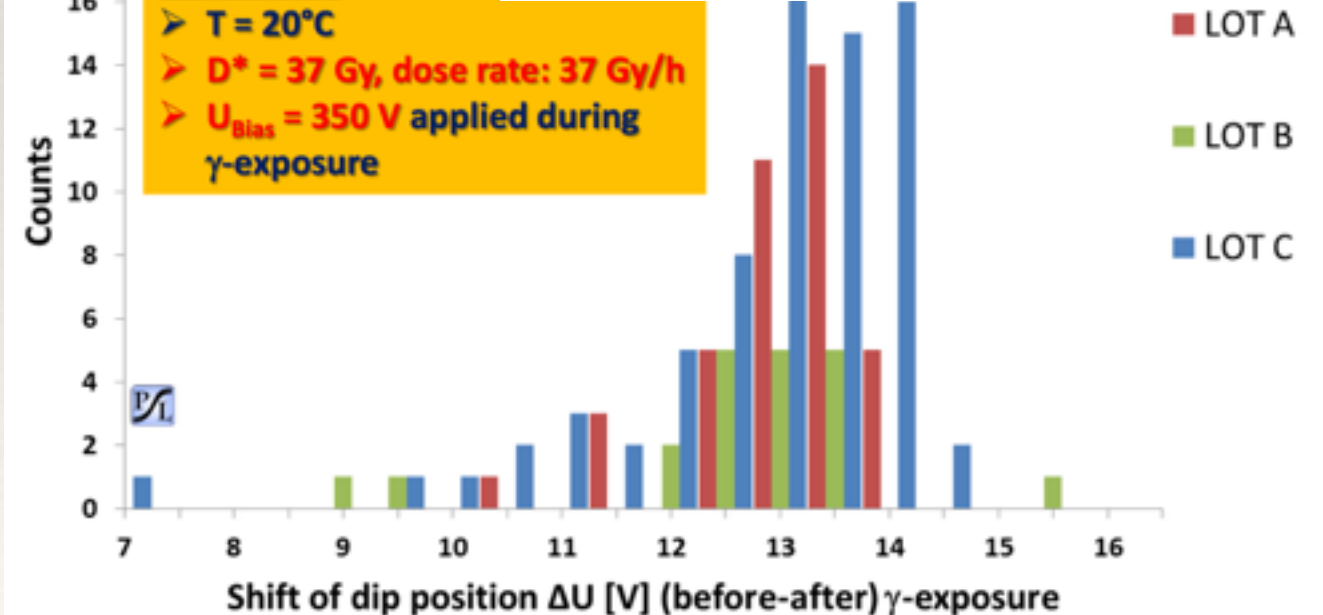


LOT de

'Structural dip': value

Conditions:

- $T = 20^\circ\text{C}$
- $D^* = 37 \text{ Gy}$ , dose rate:  $37 \text{ Gy/h}$
- $U_{bias} = 350 \text{ V}$  applied during  $\gamma$ -exposure





# MEG-II (Y. Ushiyama)

MEG II design ([EPJ-C 78\(2018\)380](#))

COBRA  
superconducting magnet

Liquid xenon photon detector  
(LXe)

$\gamma$

$e^+$

$\mu^+$

Pixelated timing counter  
(pTC)

Muon stopping target

Cylindrical drift chamber  
(CDCH)

Radiative decay counter  
(RDC)

June 12, 2018  
YUSUKE UCHIYAMA

Scintillation detectors with SiPM

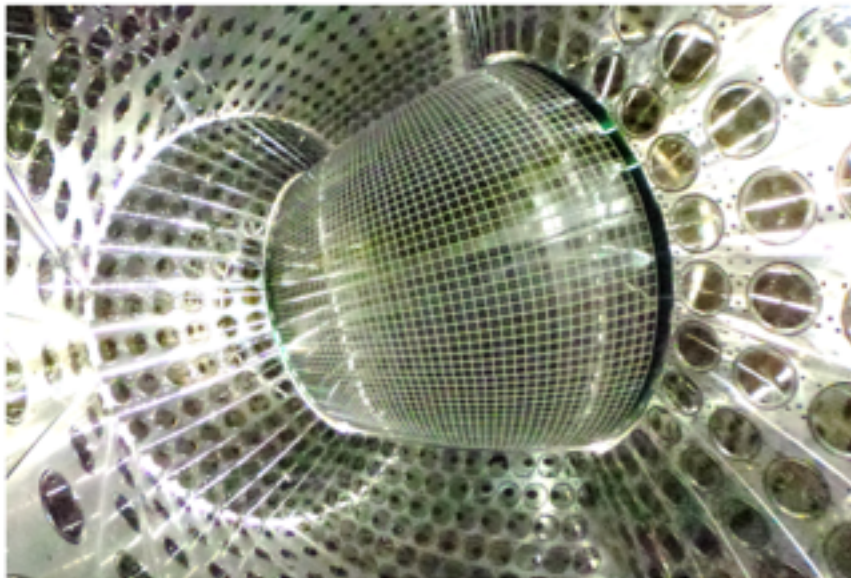
4



# MEG-II (Y. Ushiyama)

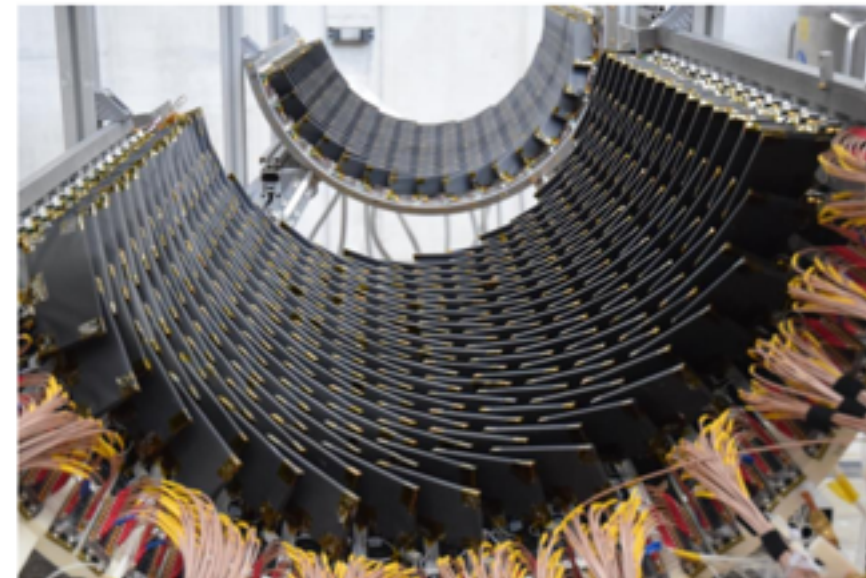
## Two large-scale SiPM-based detectors

LIQUID XENON PHOTON DETECTOR



- For  $\gamma$  energy, timing & position measurement
- SiPM for the readout of liquid xenon scint. light
- Highly granular readout (4092 ch)
- Total  $4092 \times 4 = 16368$  SiPMs
  - ❑ From Hamamatsu Photonics
  - ❑ Large size ( $12 \times 12 \text{ mm}^2$ ) by 4 chips in a package ('hybrid' connection)
  - ❑ VUV sensitive ( $\lambda = 175 \text{ nm}$ )
  - ❑ Used at low temperature ( $-100^\circ\text{C}$ )

PIXELATED TIMING COUNTER



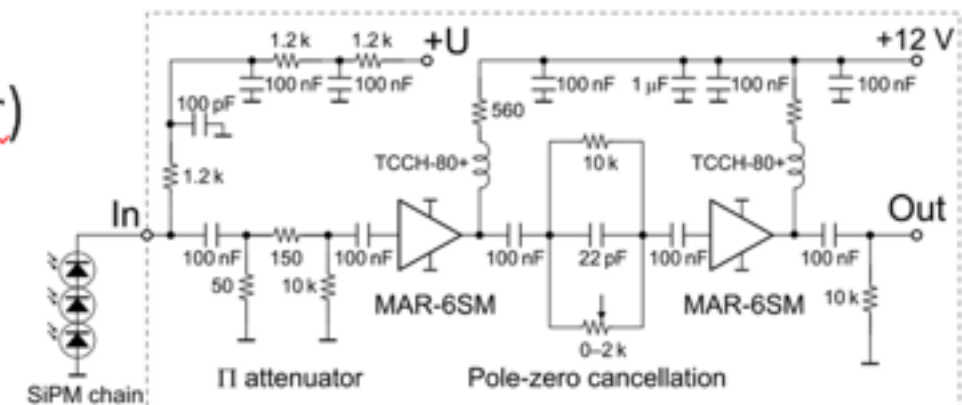
- For  $e^+$  timing measurement
- SiPM for the readout of plastic scint. counters.
- Highly segmented design (512 counters)
- 12 SiPMs/counter, 6 (series connection)  $\times$  2 sides
- Total 6144 SiPMs
  - ❑ From AdvanSiD
  - ❑  $3 \times 3 \text{ mm}^2$ , 50  $\mu\text{m}$  pitch



# MEG-II (Y. Ushiyama)

## Readout electronics in pre-tests

- During the R&D and mass test, we used standalone readout system.
- KEITHLEY picoammeter
- Amplifier developed at PSI (by U. Greuter)
- DRS4 evaluation board (by S. Ritt)
  - ❑ <https://www.psi.ch/drs/evaluation-board>
  - ❑ 4 ch waveform digitizer
  - ❑ able to daisy-chain multiple boards



USB→PC

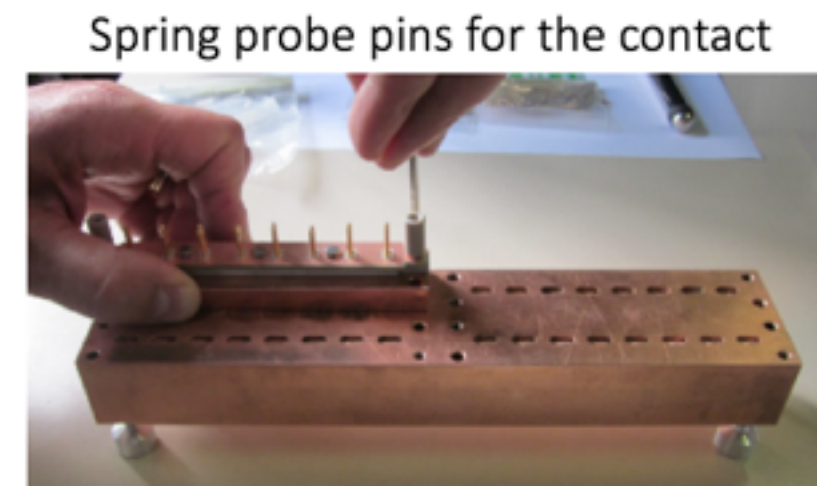
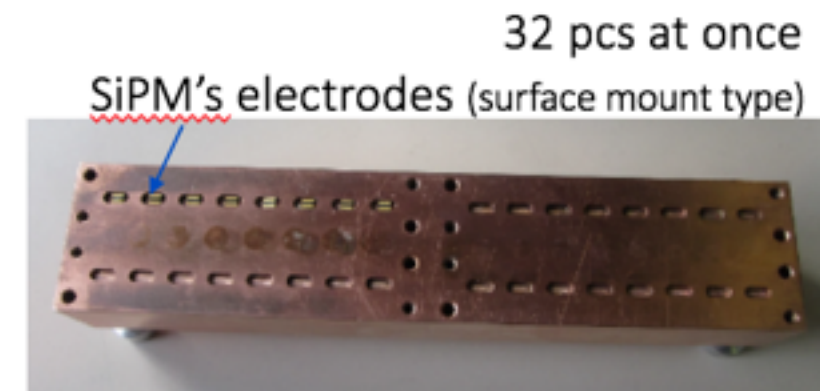
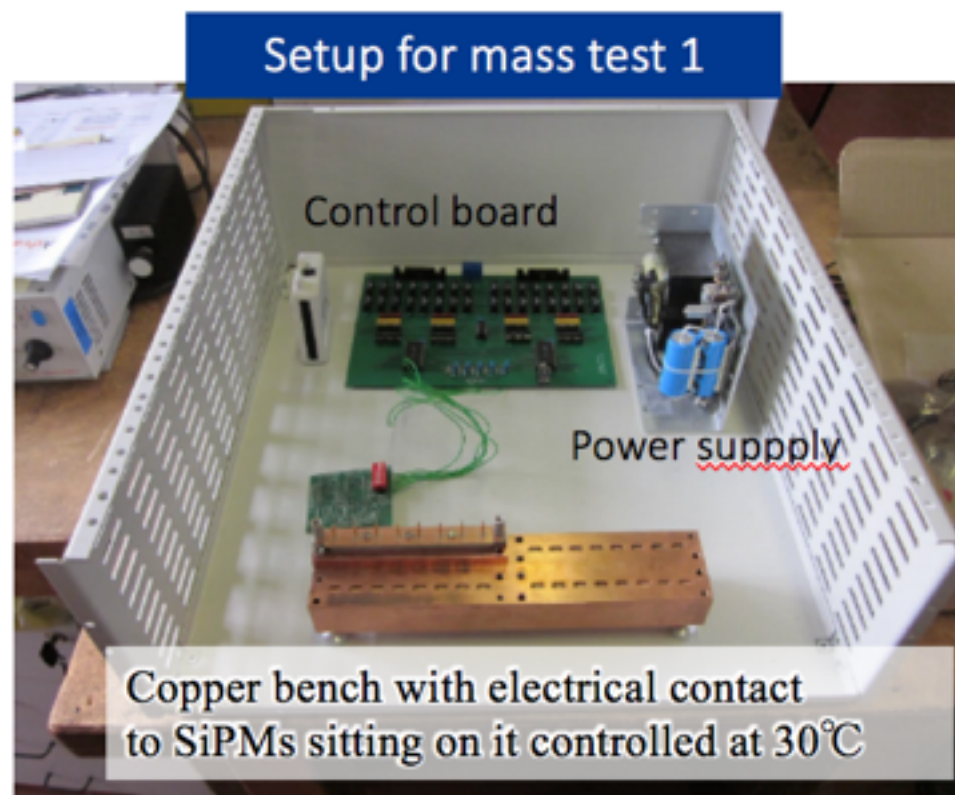


# MEG-II (Y. Ushiyama)

## Mass test 1: individual SiPM test

- To identify bad SiPMs and to group 6-SiPM sets,
- we measured  $I$ - $V$  characteristics for >7000 SiPMs.
  - Breakdown voltage ( $V_{bd}$ )
  - Leakage current @  $V_{over} = 3.0$  V ( $I_{3V}$ )

→ Group by the order of  $I_{3V}$





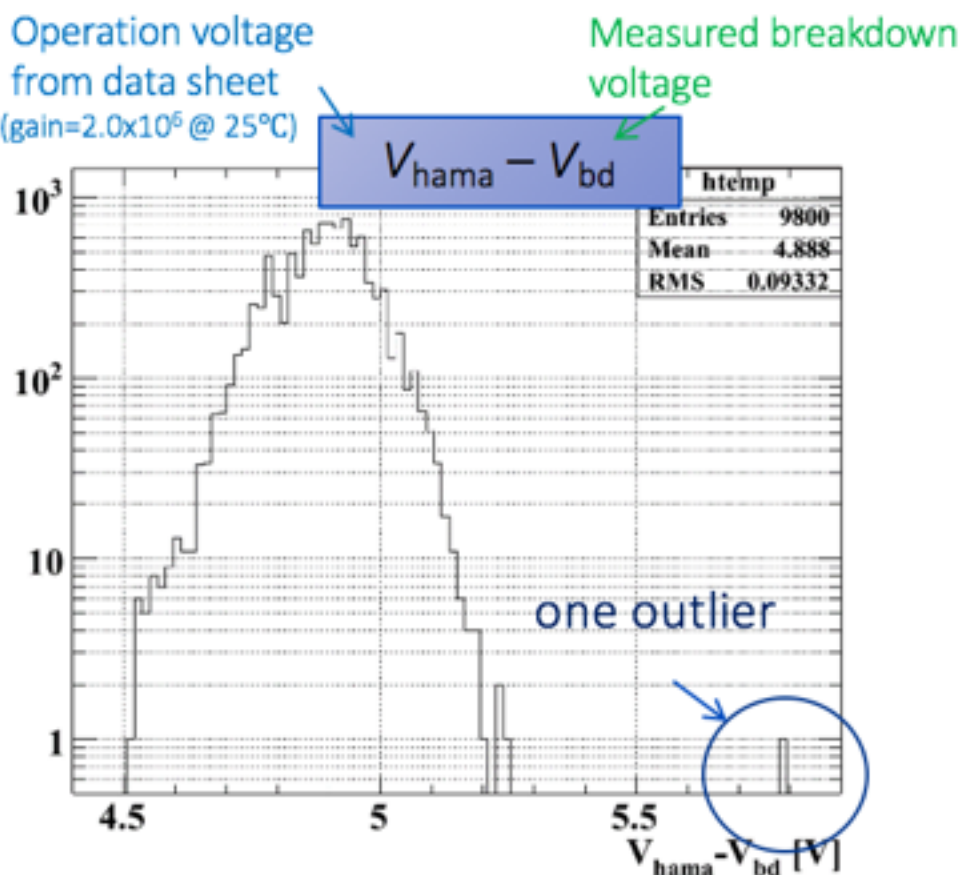
# MEG-II (Y. Ushiyama)

## Mass test 1: individual chip test

- To identify bad chips,
- we measured  $I$ - $V$  characteristics for all  $4200 \times 4$  chips.
  - Breakdown voltage ( $V_{bd}$ )
  - Leakage current @  $V_{over} = 5.0$  V ( $I_{meas}$ )
  - Shape of  $I$ - $V$  curve

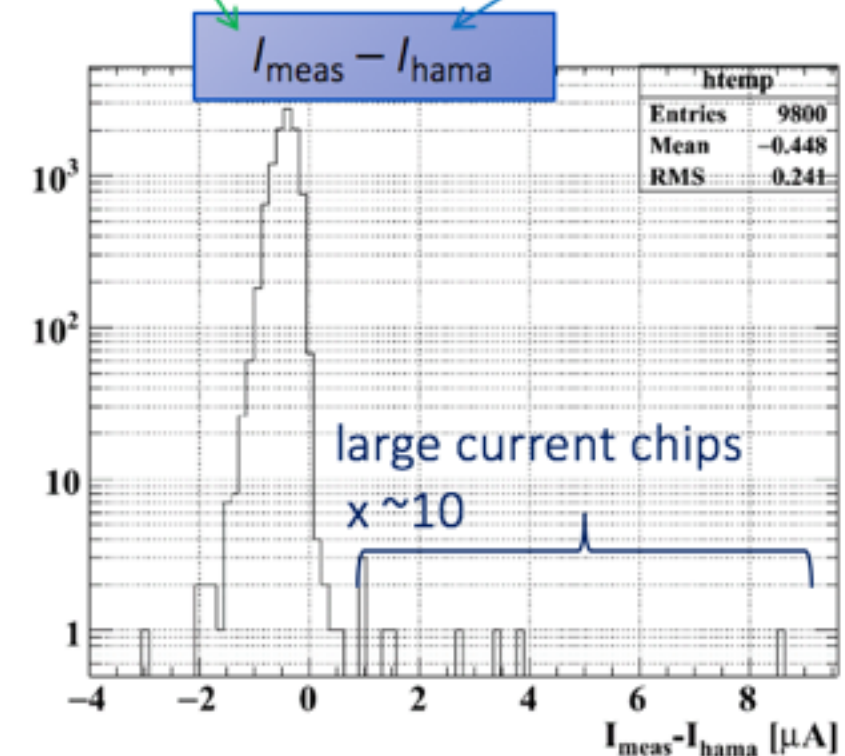
→ compare with the data sheet ( $V_{hama}$ ,  $I_{hama}$ )

Operation voltage  
from data sheet  
(gain= $2.0 \times 10^6$  @  $25^\circ\text{C}$ )



Measured current at  $V = V_{bd} + 5.0$  V

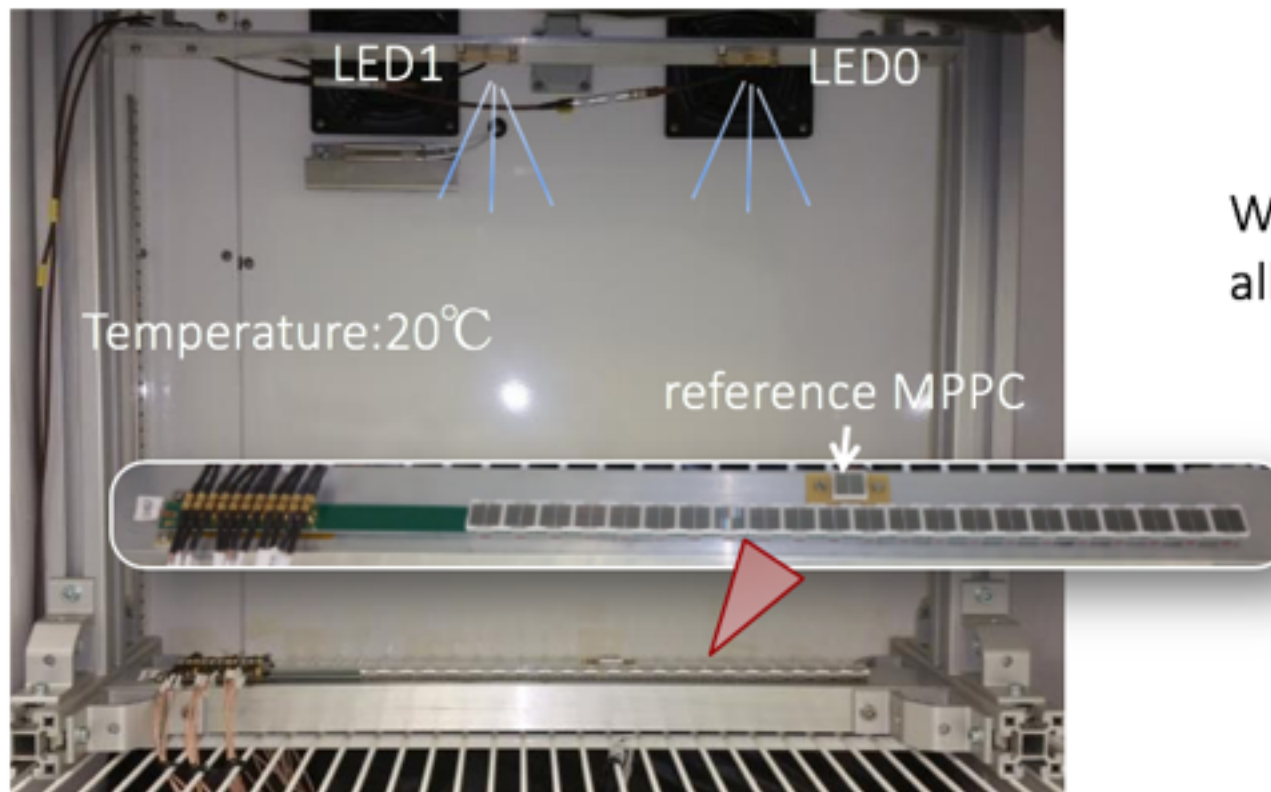
Current at  $V_{hama}$  from data sheet



# MEG-II (Y. Ushiyama)

## Mass test 2: MPPC test on PCB

- To test MPPC signals



Waveform and charge were measured for all MPPCs on every PCB.

Data taking with strong LED light

$V = V_{\text{hama}}$  (operation voltage from spec. sheet,  $V_{\text{over}} \sim 5\text{V}$ )

MPPC mounting + test =  $\sim 15\text{min/PCB}$

186 PCBs  $\rightarrow \sim 47\text{hours}$  in total

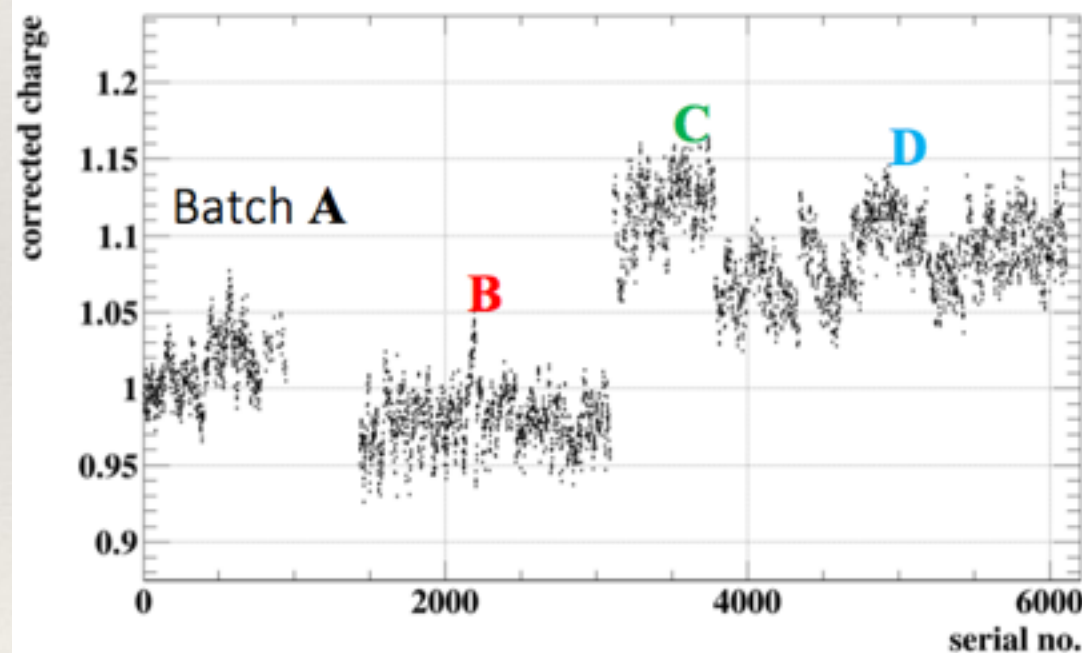


# MEG-II (Y. Ushiyama)

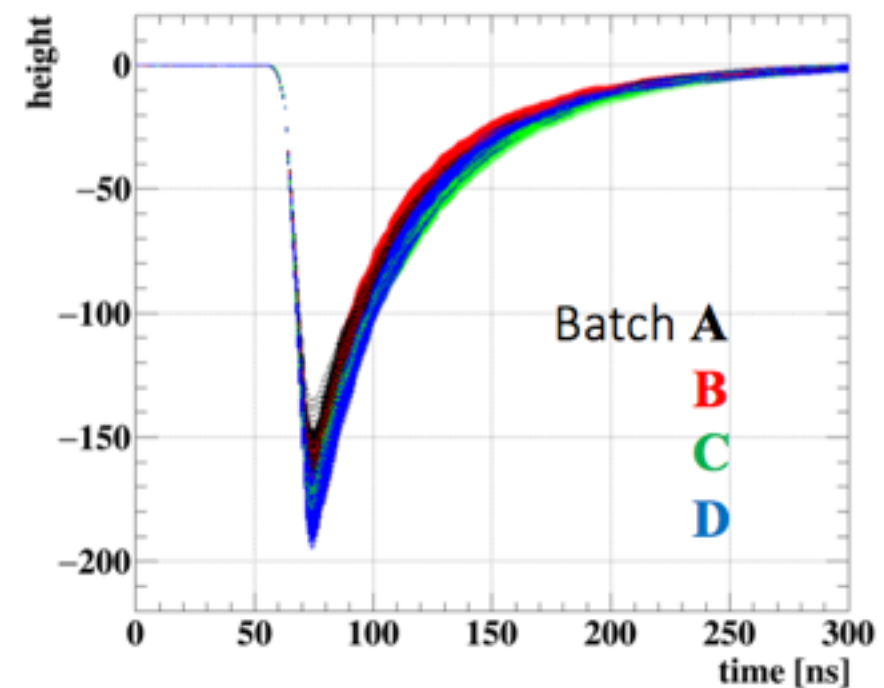
## Mass test 2: MPPC test on PCB

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Vertical axis is **charge** normalized by charge of a MPPC in batch A.



Waveform of 4092 MPPCs overlaid.



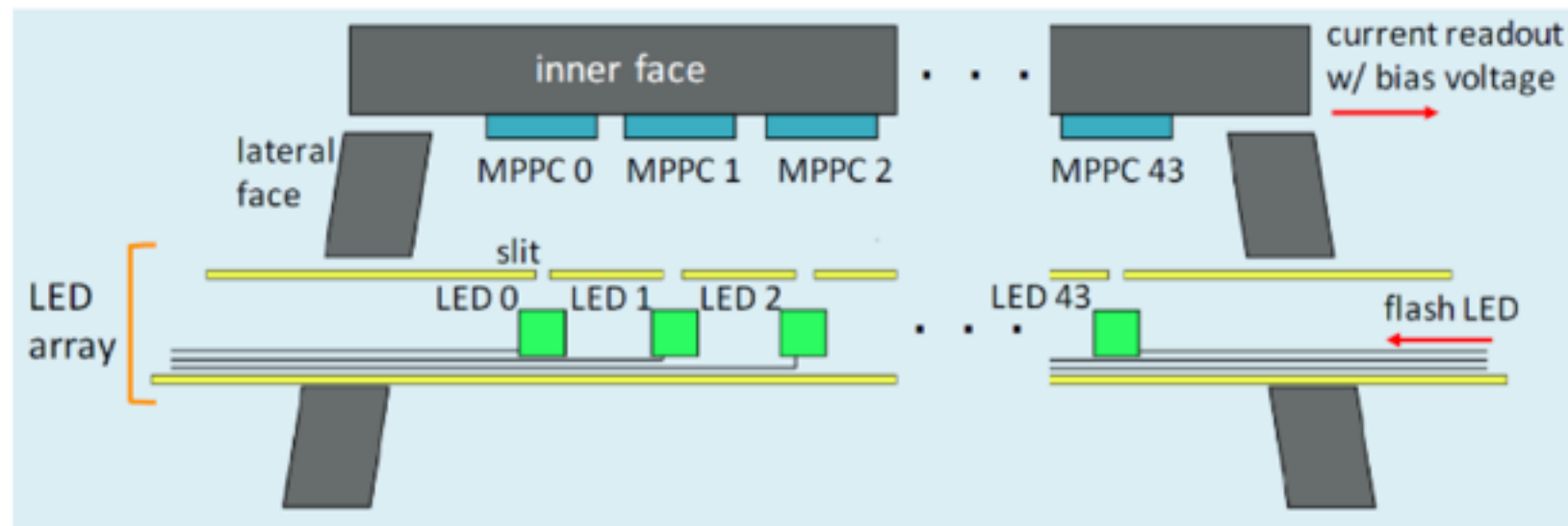
All channels are good.

Batch by batch difference is found, due to difference in afterpulse probability.

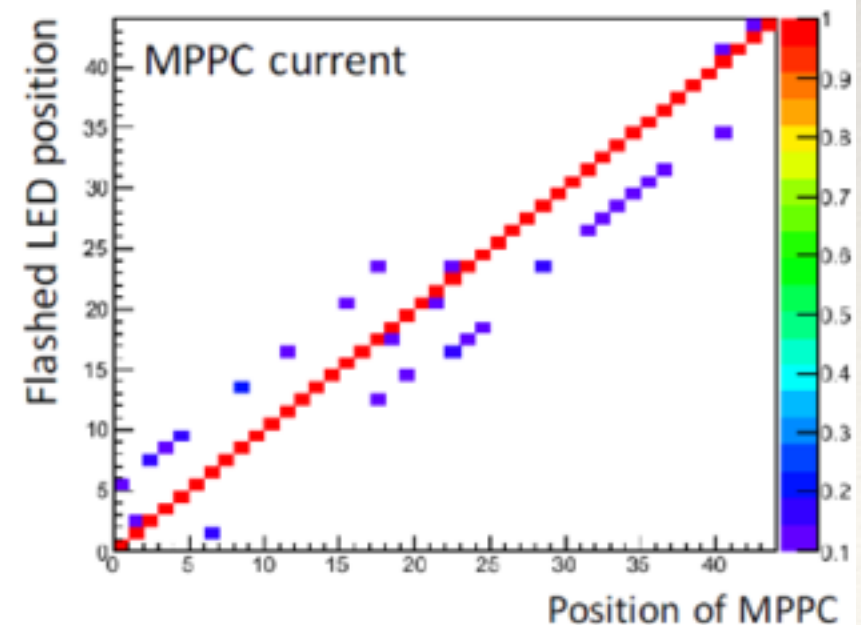
# MEG-II (Y. Ushiyama)

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## Signal check during construction



- To check cabling and connection,
- measure the MPPC currents with flashing LEDs in array one-by-one and check the correspondence.



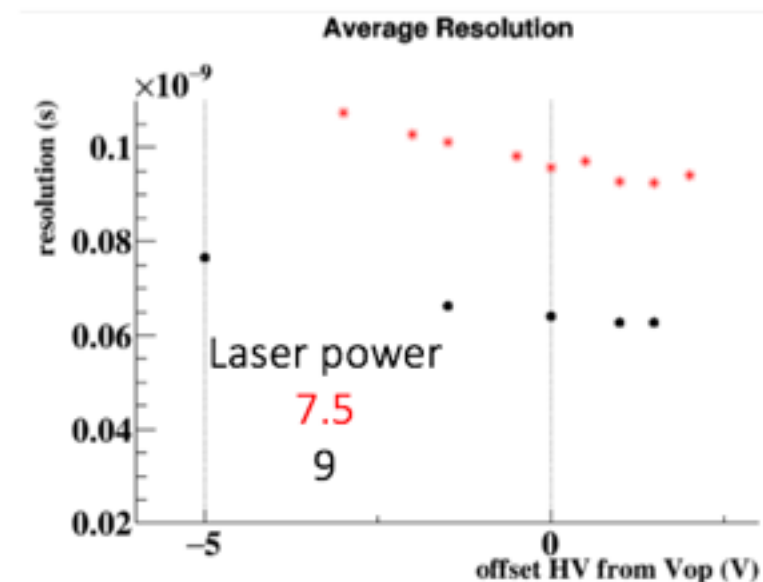
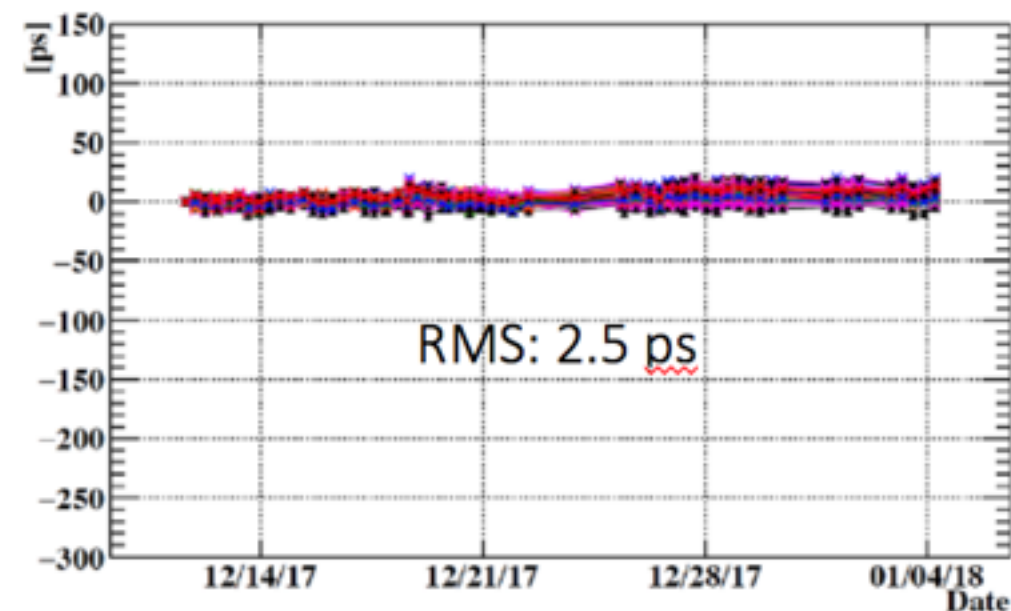




# MEG-II (Y. Ushiyama)

## Calibration & optimization with laser

- Calibrate time offset of each counter with the synchronous laser pulse signal.
- Monitor the timing (time offset) with the laser pulse over time.
  - also the pulse amplitude ( $\propto G \times \text{PDE}$ )
- Optimize the bias voltage for the best timing resolution.
  - under a real noise condition.





# MEG-II (Y. Ushiyama)

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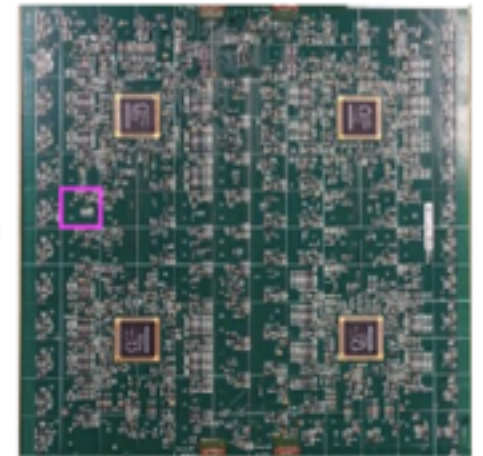
## Conclusions

- We established methods for mass test and calibration.
  - ❑ Total inspection with a quick method is important before detector construction.
    - reject bad sensors, optimize combinations/arrangement etc.
  - ❑ Detailed characterization before experiment is important to understand the detector.
  - ❑ Continuous monitoring of SiPM parameters is important during the experiment to maximize the performance.
    - temperature change, radiation damage, etc.
- Standardization makes little (no) sense once detector is built
  - ❑ Necessity is different b/w detector R&D/designing and operation/calibration.
  - ❑ We can/should only & all what we can do within the constraints of experiment.
- Quality control in mass-production is important
  - ❑ Not only to guarantee the high performance,
  - ❑ but also to make the analysis & calibration easy.
  - ❑ Hope manufacturers to improve this.

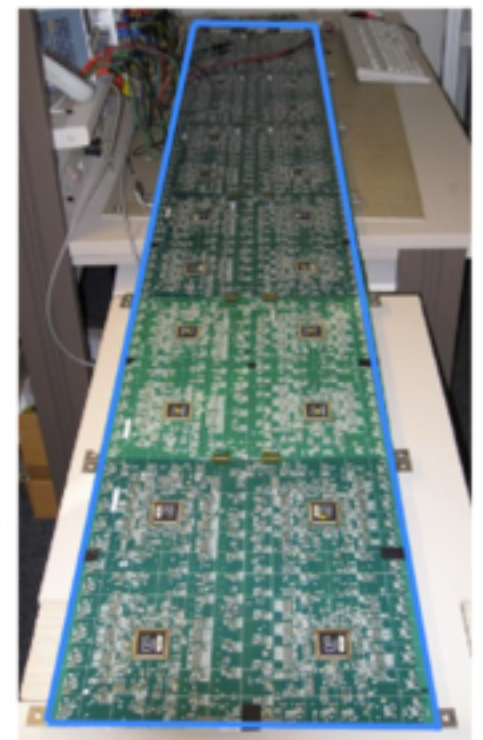
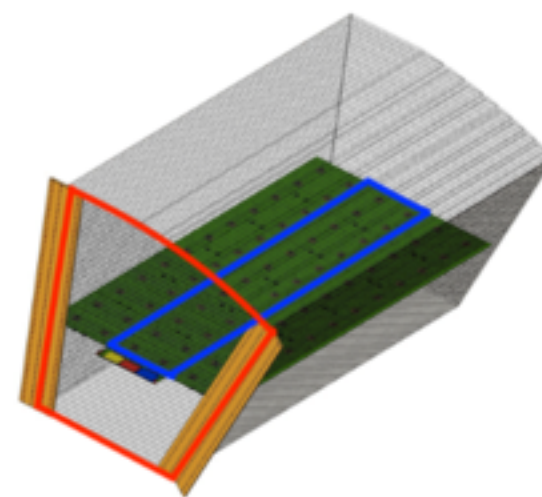
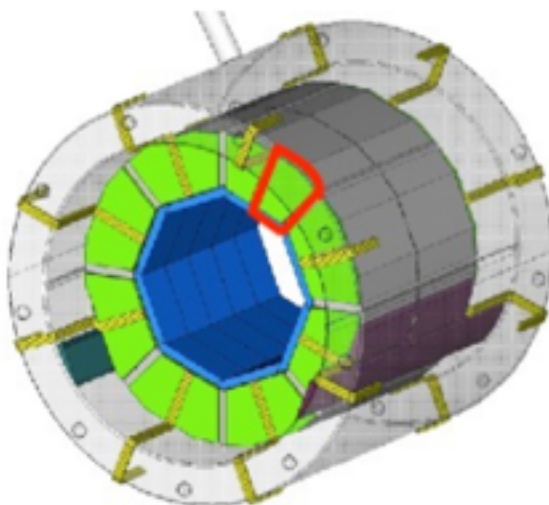
# CALICE (Y. Munwes)

## Scintillator based hadronic calorimeter (AHCAL)

- Sandwich calorimeter based on scintillator tiles ( $3 \times 3 \text{ cm}^2$ ) readout using SiPMs
- Fully integrated electronics
- HCAL Base Unit (HBU):  $36 \times 36 \text{ cm}^2$ , 144 channels, 4 ASICS
- High granularity: **8M** channels
- Technological prototype: demonstrate **scalability** to full detector



**24 000 SiPMs for prototype!**

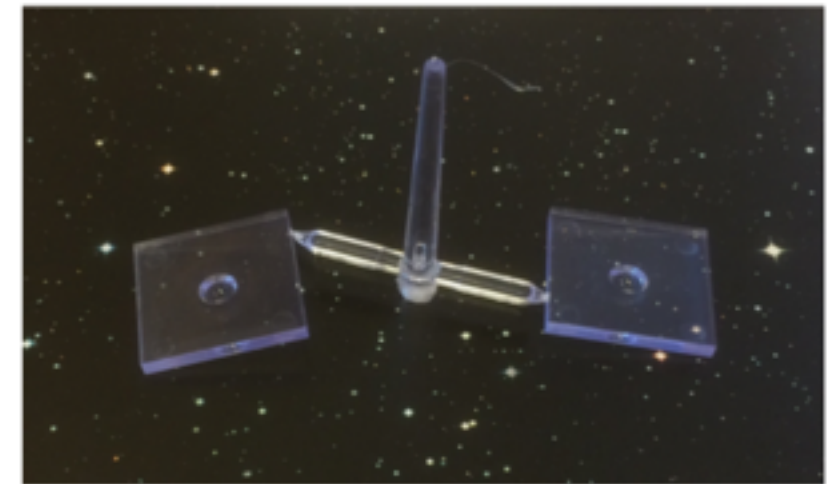
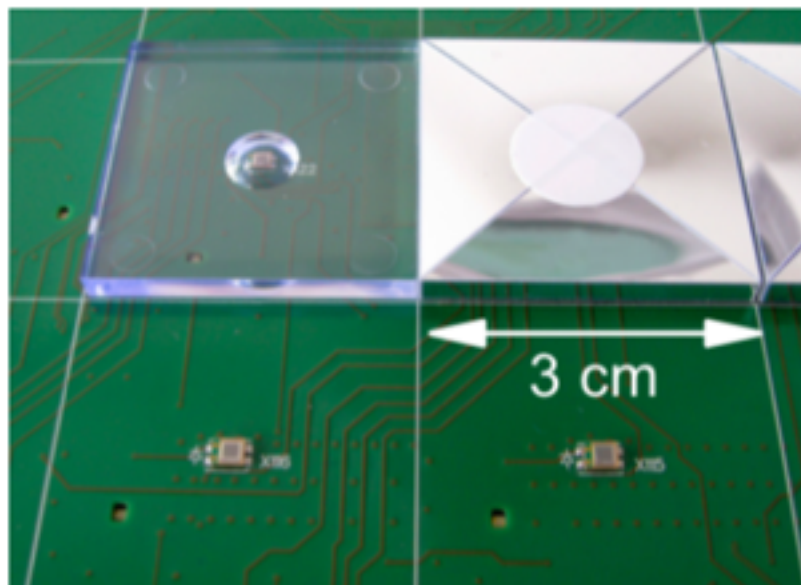




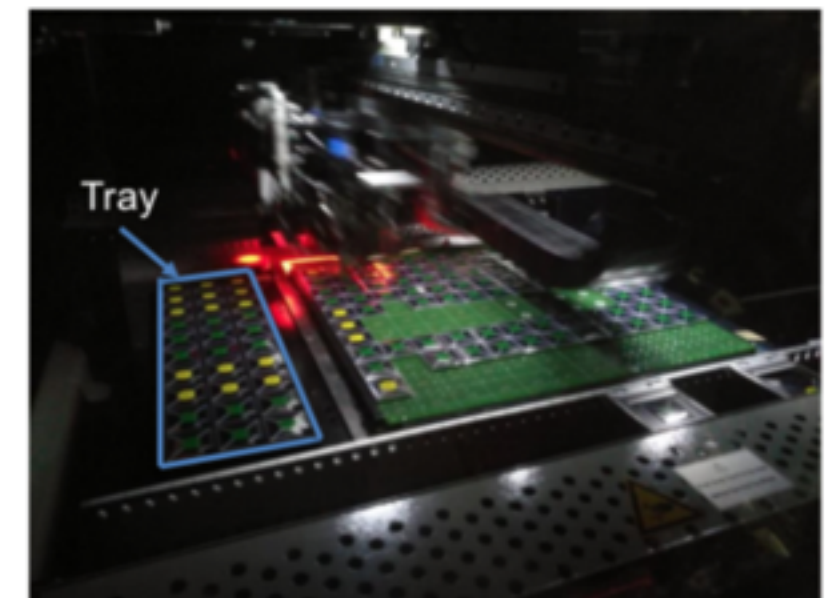
# CALICE (Y. Munwes)

## New detector design

- SMD SiPM → directly soldered on the HBU
- Simpler tile design  
→ allow injecting moulding (tile/min, Lebedev Physics Institute)
- Tile wrapping using fully automatic machine (Uni. Hamburg)
- Tile assembly using pick and place machine (Uni. Mainz)



*Injected mould tiles*



*Automatic placing of tiles*

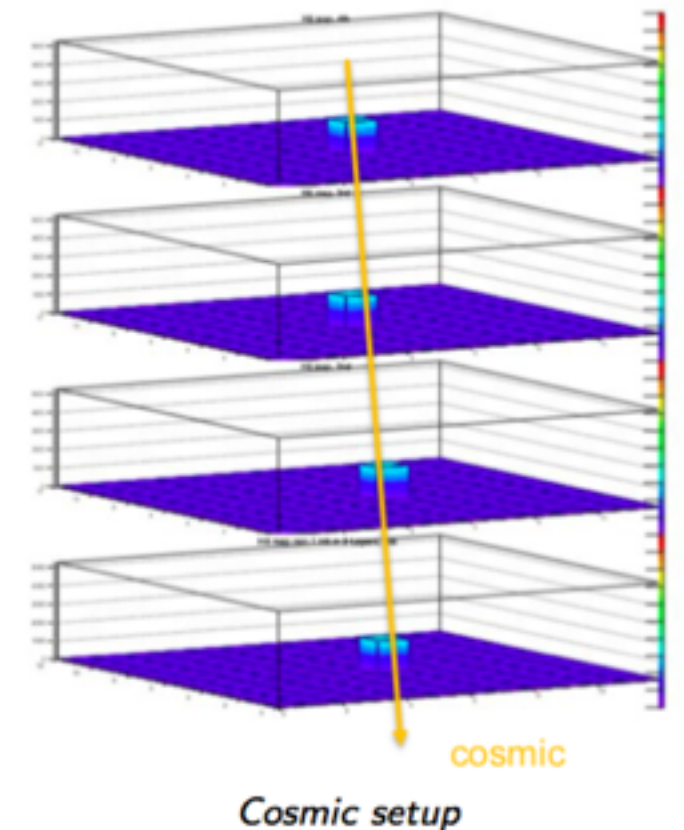
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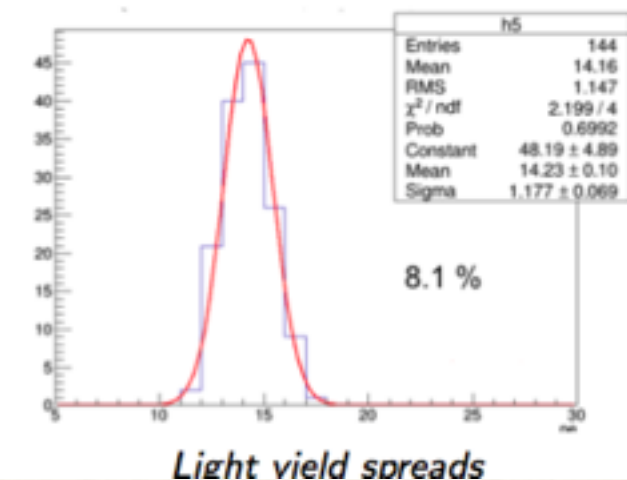
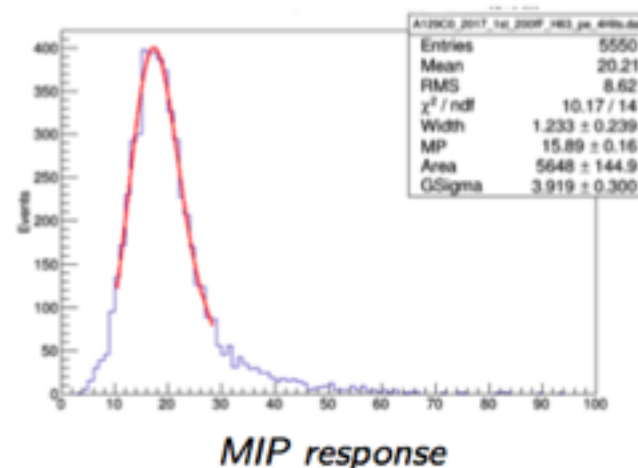
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### QA tests in two steps

- SiPM QA before soldering
- Test tile+SiPM after assembly (Mainz University)



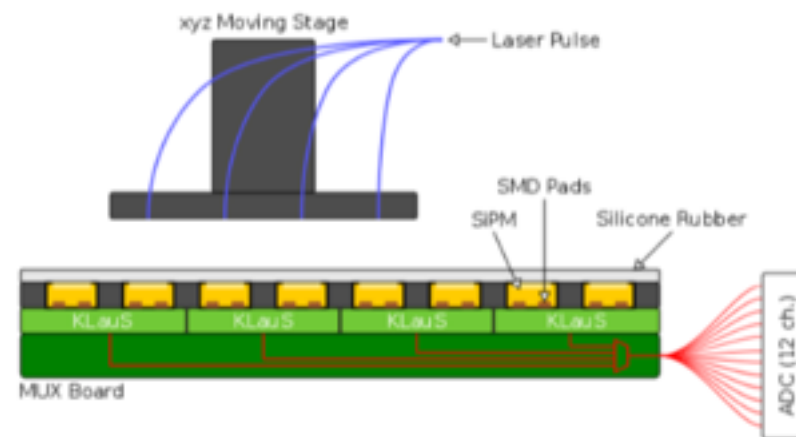
**Stable  
temperature!**



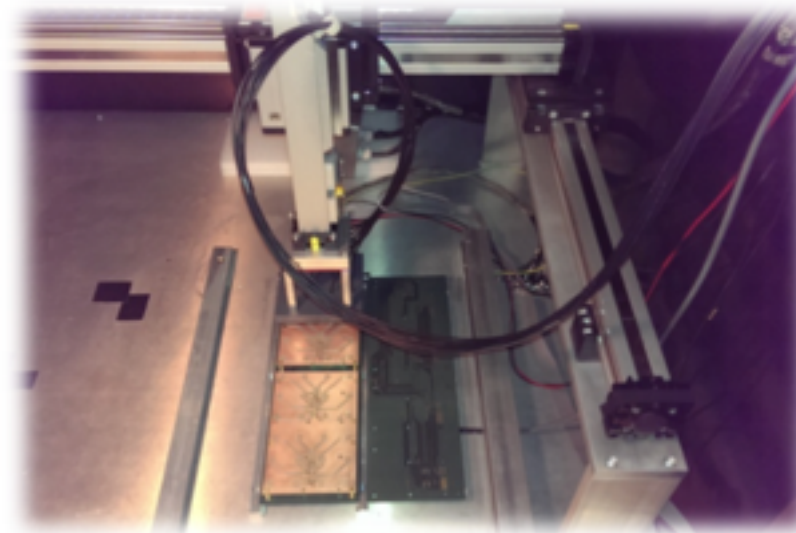


# CALICE (Y. Munwes)

- 24 SiPMs
- Multiplex PCB
- 2 Klaus ASICs



*SMD SiPM schematic view*



Splitting Laser light

48 SMD SiPMs without soldering

NO PDE measurement!

# CALICE (Y. Munwes)

## Measurement procedure

### Measurement:

- Using low intensity light spectra
- The setup is inside an oven with constant temperature of 25°C
- Measure the SPS spectrum for voltage range of 1 V to 7 V above breakdown (Hamamatsu datasheet) at step size of 0.1 V
- For the sample measured during night re-measure for temperatures (10,15,20,25,30,35,40°C)

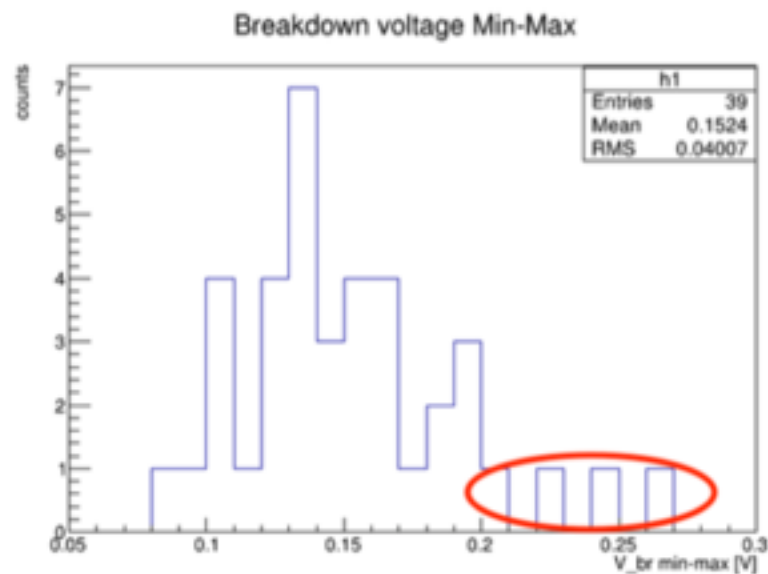
### Analysis:

- Extract from each SPS spectrum the gain using FFT
- Extract the breakdown voltage for each temperature and SiPM from linear fit of gain vs. voltage
- Estimate the DCR from SPS using Poisson statistics:  $DCR = -\ln\left(\frac{N_0}{N_{tot}}/\Delta t\right)$  (1)
- Estimate CT upper limit from the DCR spectrum
- extract for each SiPM the temperature coefficient from linear fit of the breakdown voltage vs. temperature (for available samples)

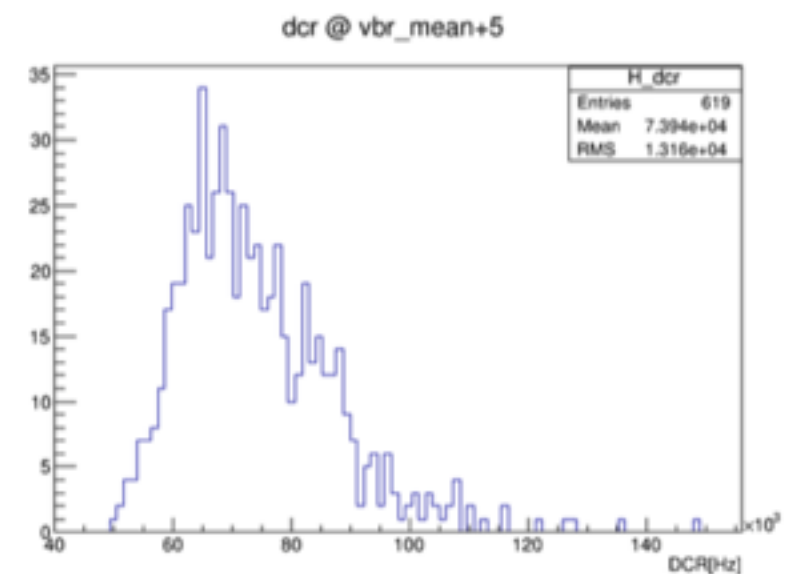
\* the gain is measured in arbitrary units  $\rightarrow 13 \sim 3 \times 10^5$  (the requirement)



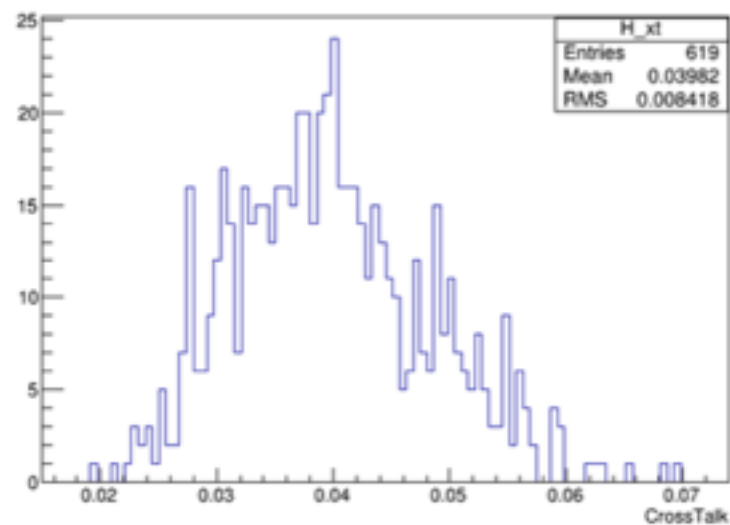
# CALICE (Y. Munwes)



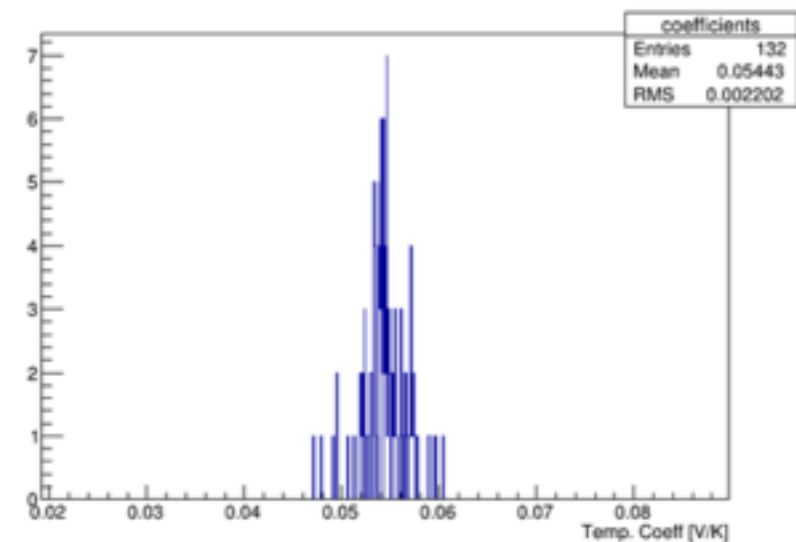
*breakdown voltage min-max spread*  
xt @ vbr\_mean+5



*DCR spread*



*Cross-talk spread*

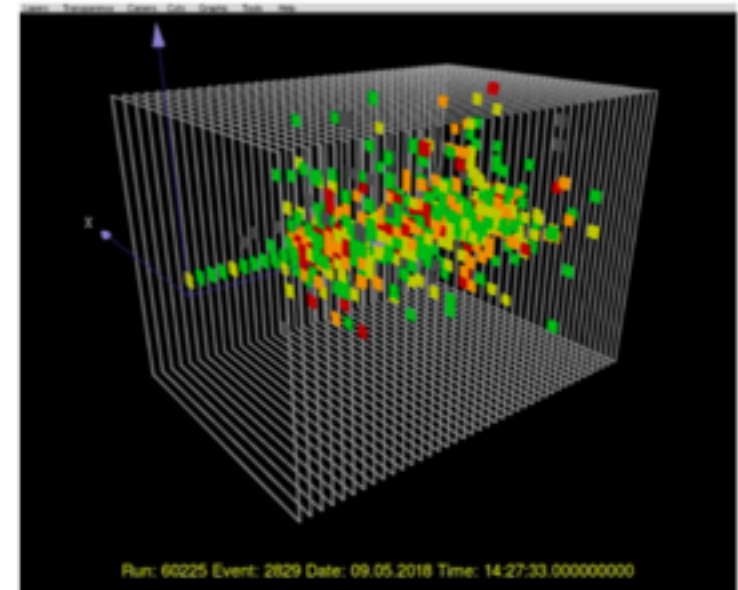
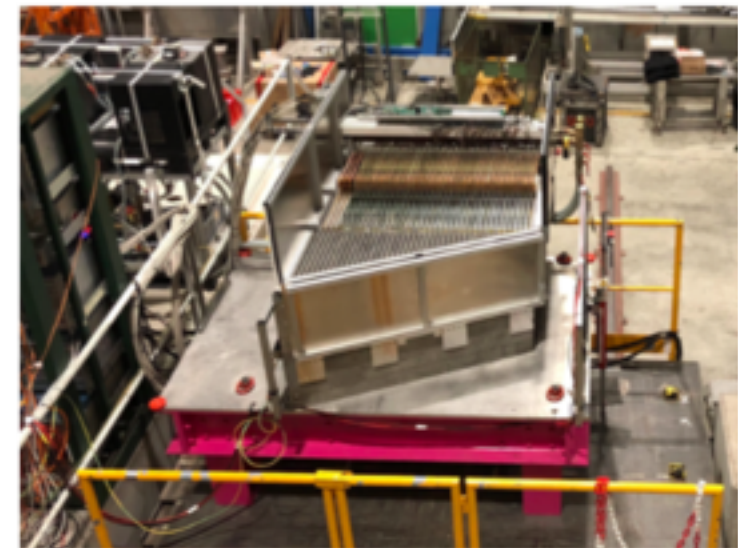


*Temperature coefficient spread*

# CALICE (Y. Munwes)

## Summary

- A large scale engineering prototype was build this year (24k channels)
- New test benches for QA of SMD SiPMs were designed
- Test benches are easily scaled up
- Fast SiPM characterization ( $\sim 10$  sec per SiPM)
- All SiPM batches passed the requirements
- Good uniformity in SiPM parameters observed
  - Will allow to test less SiPM in the future
- Small non linearity in gain curves didn't bias the spread measurement
- For large scale version, an active cooling will be designed



KIRCHHOFF-  
INSTITUTE  
FOR PHYSICS



This project has received funding from the European Union's Horizon 2020 Research and Innovation programme under Grant Agreement no. 654168.



AIDA<sup>2020</sup>

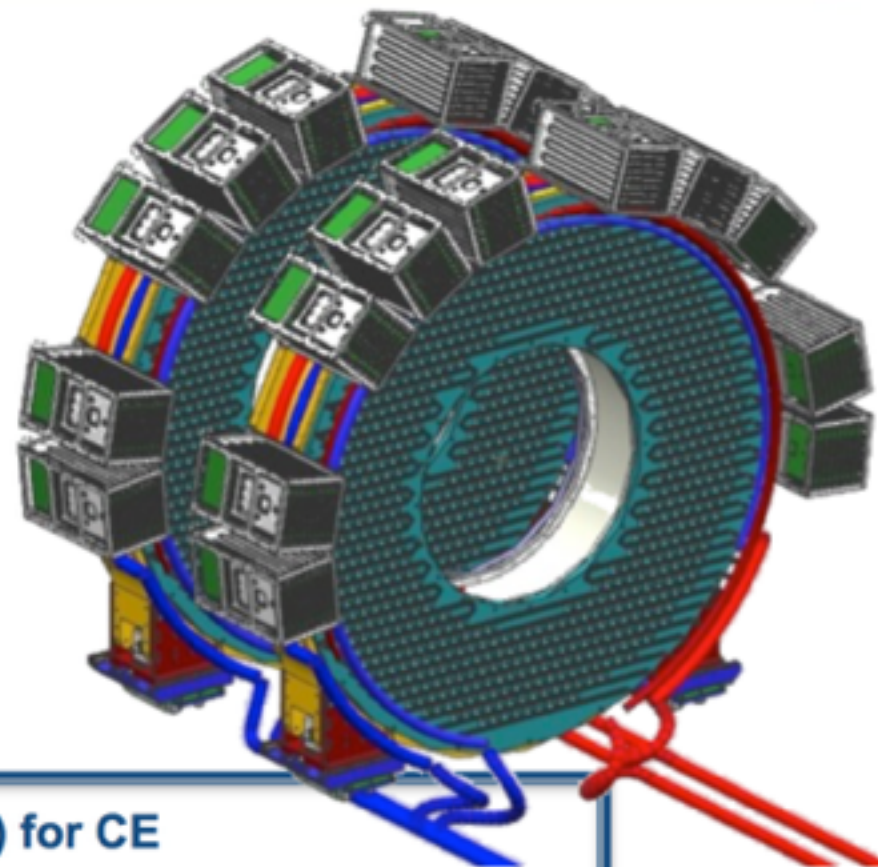


# Mu2e (I. Sarra)

## Calorimeter Summary

2 annular disks with 674  
undoped Csl (34 x 34 x 200) mm<sup>3</sup>  
square crystals/each disk

- Operate in 1 T and in vacuum at 10<sup>-4</sup> Torr
- R<sub>IN</sub> = 374 mm, R<sub>OUT</sub> = 660 mm
- Depth = 10 X<sub>0</sub> (200 mm), Distance 70 cm
- Redundant readout:  
**2 UV-extended SiPMs/crystal**
- **RA source for energy calibration**
- **Laser system for monitoring**



Total Number  
of SiPMs arrays  
(3x2 SiPMs)

~ 1348x2 = 2696  
arrays

Array works  
as a whole

### Requirements @ 105 MeV/c

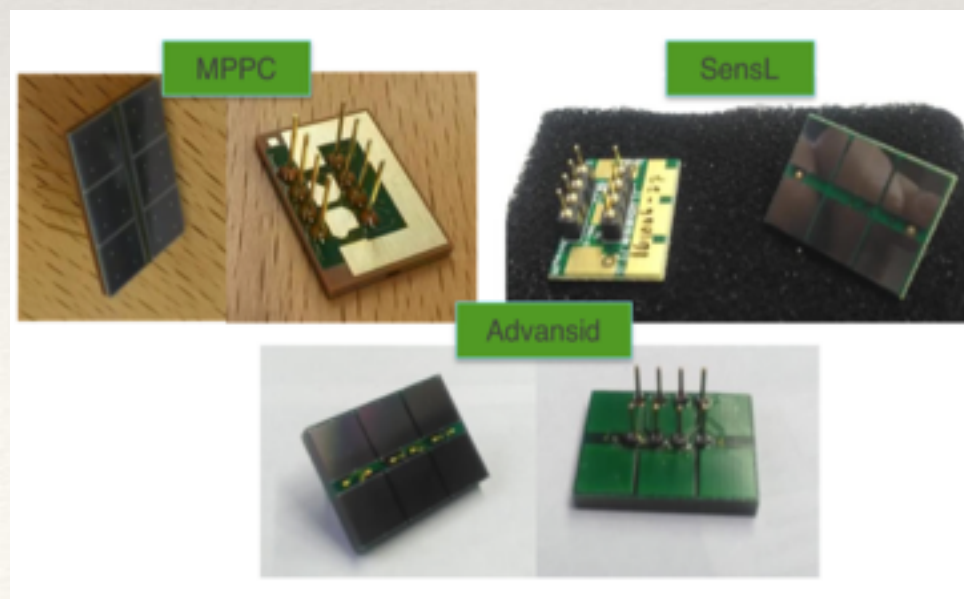
- $\sigma_E/E = \mathcal{O}(10\%)$  for CE
- $\sigma_T < 500$  ps for CE
- $\sigma_{X,Y} \leq 1$  cm
- Fast scintillation signals ( $\tau < 40$  ns)
- Radiation hardness (with a safety factor of 3):
  - 100 krad (45 krad) dose for crystals
  - $3 \times 10^{12} n_{1\text{MeV}}/\text{cm}^2$  for crystals



# Mu2e (I. Sarra)

50 samples  
from each company

- 1) a high gain, above  $10^6$ , for each monolithic ( $6 \times 6$ ) mm<sup>2</sup> SiPM cell;
- 2) a good photon detection efficiency (PDE) of above 20% at 310 nm to well match the light emitted by the undoped CsI crystals;
- 3) a large active area that, in combination with the PDE, could provide a light yield of above 20 p.e./MeV;
- 4) a fast rise time and a narrow signal width to improve time resolution and pileup rejection;
- 5) a Mean to Time Failure (MTTF) of  $O(10^6)$  hours;
- 6) and a good resilience to neutrons for a total fluency up to  $10^{12}$  n-1MeV<sub>eq</sub>/cm<sup>2</sup>.



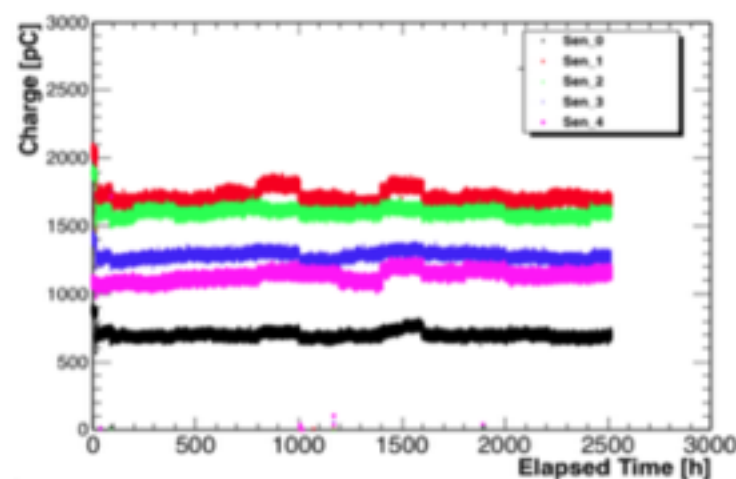


# Mu2e (I. Sarra)

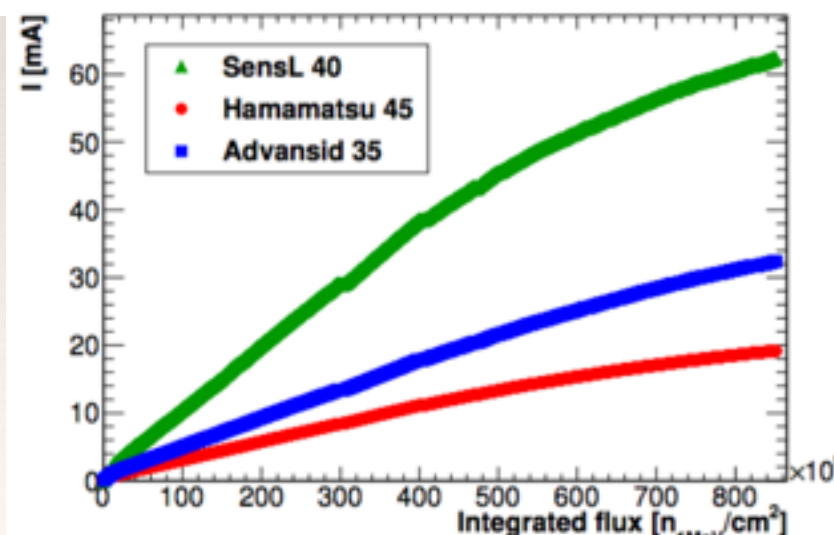
➤ 150 SiPM arrays where fully characterized with a semi-automatized station:

	Hamamatsu	SensL	AdvanSid
$V_{br}$	$(51.85 \pm 0.11) \text{ V}$	$(24.87 \pm 0.06) \text{ V}$	$(27.20 \pm 0.04) \text{ V}$
$\text{RMS}(V_{br})$	$(0.070 \pm 0.005)\%$	$(0.13 \pm 0.01)\%$	$(0.11 \pm 0.01)\%$
$I_{dark}$	$(0.77 \pm 0.13) \mu\text{A}$	$(1.22 \pm 0.28) \mu\text{A}$	$(1.07 \pm 0.08) \mu\text{A}$
$\text{RMS}(I_{dark})$	$(6.4 \pm 0.5)\%$	$(8.1 \pm 0.8)\%$	$(4.7 \pm 0.4)\%$
Gain in 150 ns	$(2.40 \pm 0.01) \cdot 10^6$	$(1.92 \pm 0.01) \cdot 10^6$	$(1.10 \pm 0.05) \cdot 10^6$
$\text{RMS}(\text{Gain})$	$(1.7 \pm 0.2)\%$	$(4.3 \pm 0.5)\%$	$(8.5 \pm 0.7)\%$
PDE @ 315 nm	$(28.0 \pm 1.2)\%$	$(32.4 \pm 1.4)\%$	$(21.3 \pm 0.9)\%$

all of them satisfied the Mu2e technical requirements.



@50 deg = MTTF  $10^6$  hours!



Neutron flux up to  $10^{12}$

**Hamamatsu  
won the test!**

# Mu2e (I. Sarra)

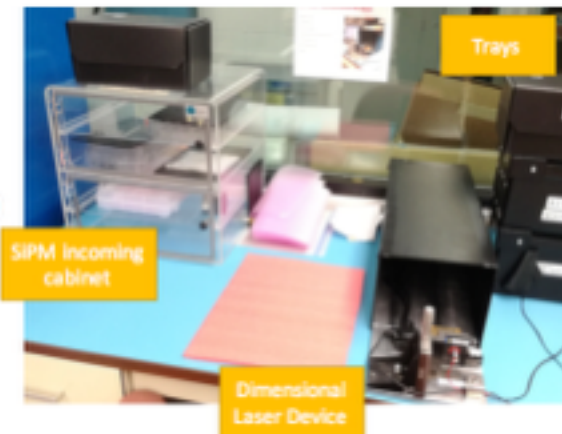
## QA Laboratory Layout

- 1: Shipping station
- h: SiPM incoming cabinet
- 5: SiPM mechanic and dimensional station
- 6: SiPM QA station
- 7: SiPM MTTF station
- K: SiPM storage drawers



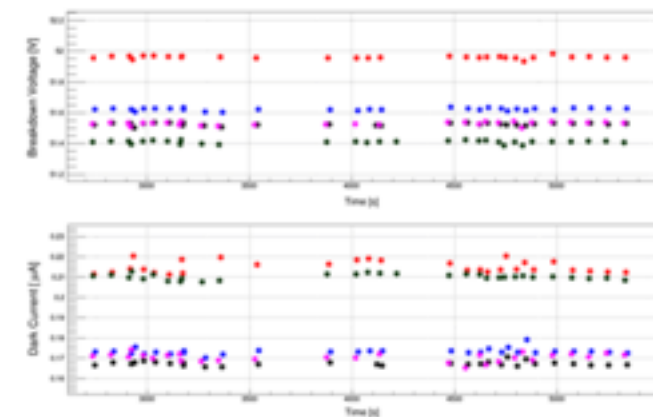
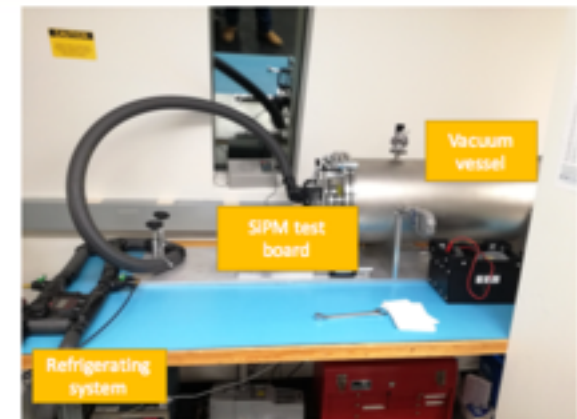
## SiPM mechanical and dimensional station

- Integrity and damages check
- Measuring of SiPM dimensions (transversal dimensions and thickness)
- Go, not-go gauge test station



## SiPM QA station

- Characterization of dark current
- Characterization of break down voltage
- Characterization of gain x PDE
- Temperatures:  $-10^{\circ}\text{C}$ ,  $0^{\circ}\text{C}$ ,  $20^{\circ}\text{C}$
- 20 SiPMs at time
- 15 hours per test
- 5 SiPMs as reference sensors

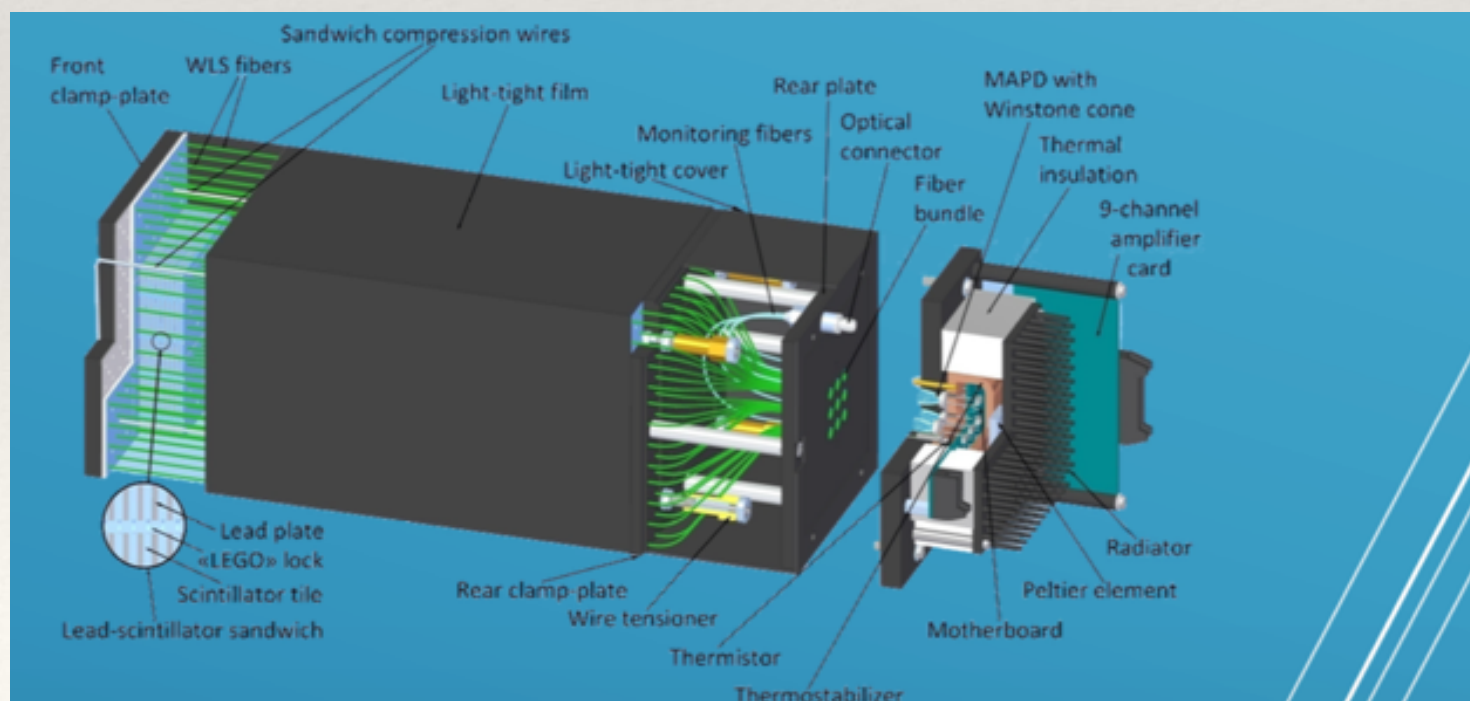
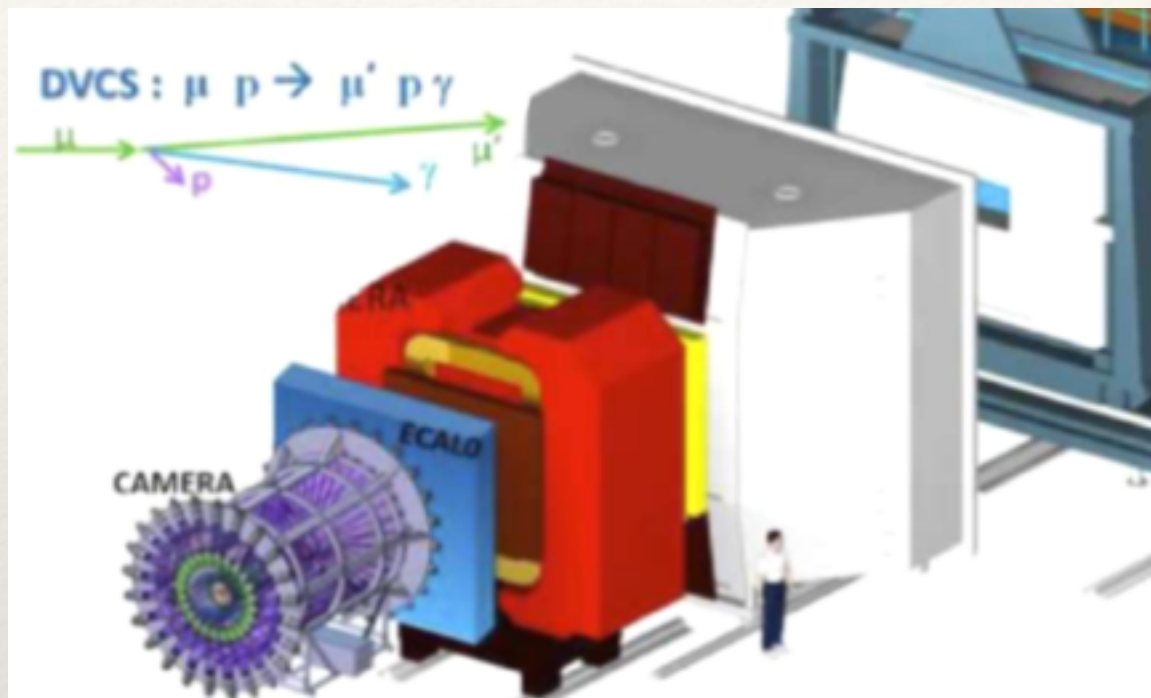


**From March 2018 1100 SiPMs were characterized!**

- ~ 300 pieces/month from March 2018
- All the 6 cells tested, measuring  $V_{br}$ ,  $I_{dark}$ , **Gain x PDE**
- 3 % of tested SiPMs rejected (defective or with high  $I_{dark}$ )



# COMPASS (A.Rybnikov)



~2000 SiPMs

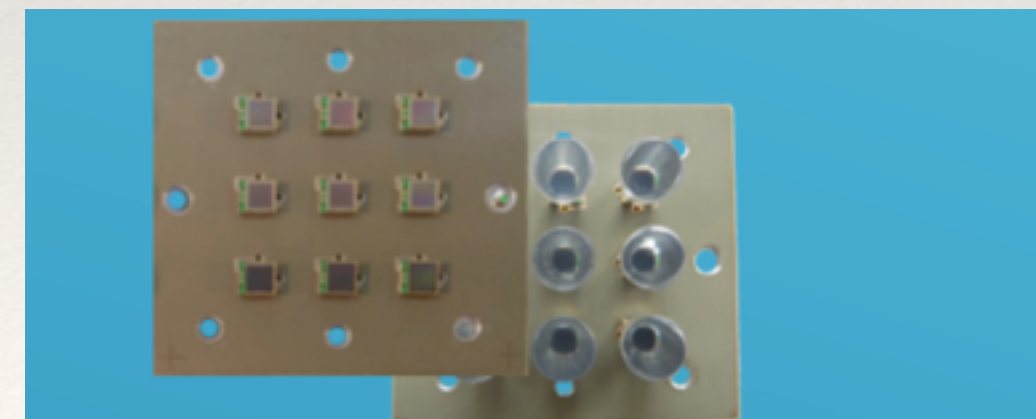


Fig.2.3: Optical module with glued SiPMs

# COMPASS (A. Rybnikov)

**The characterization can be divided into the following stages:**

## 1. The defining of SiPMs operation voltage:

The first step was to define an operation voltage corresponding to the gain of  $1.4 \times 10^5$  for each SiPM individually. To obtain the voltage we measured and evaluated the gain at different voltages with 0.2V step by using relatively high light intensity ( $\sim 100$  ph.e.)

The data and the charge spectra were acquired for 5 voltage values for each SiPM (fig.3.2). The basic idea of the gain evaluation from charge spectra is shown on the fig.3.1.

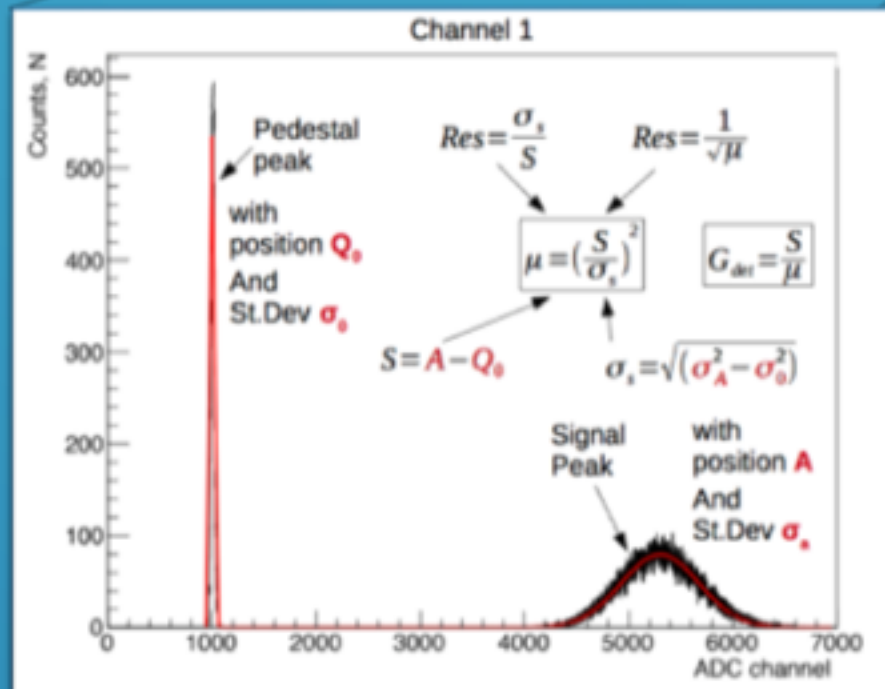


Fig.3.1: Analysis of a charge spectrum with high intensity light

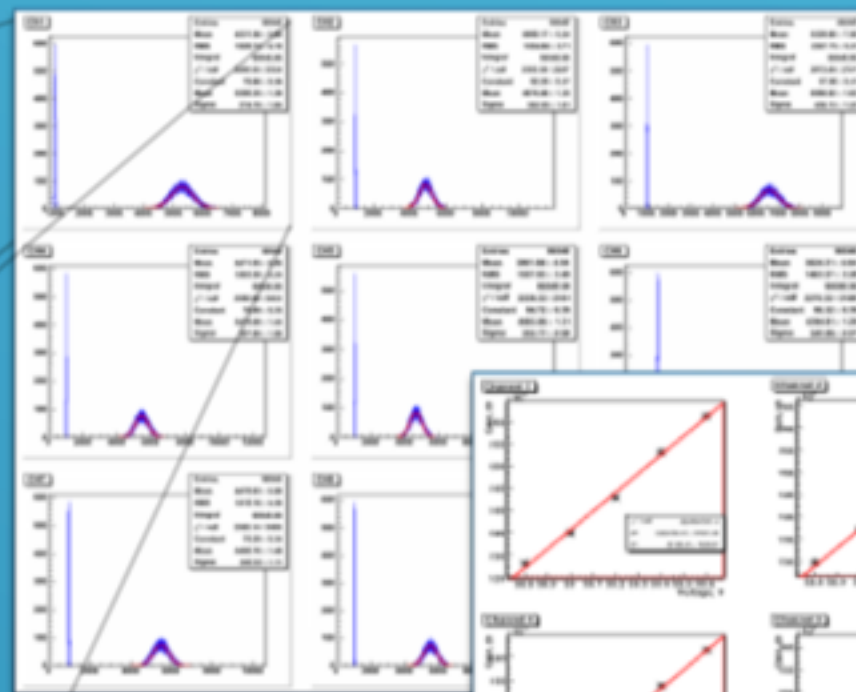


Fig.3.2: Charge spectra with high intensity light

The analysis was fully automatical. Total calibration time is ~15 minutes per module (9 SiPMs)

Each "Gain vs Voltage" relation was fitted by linear function (fig.3.3).

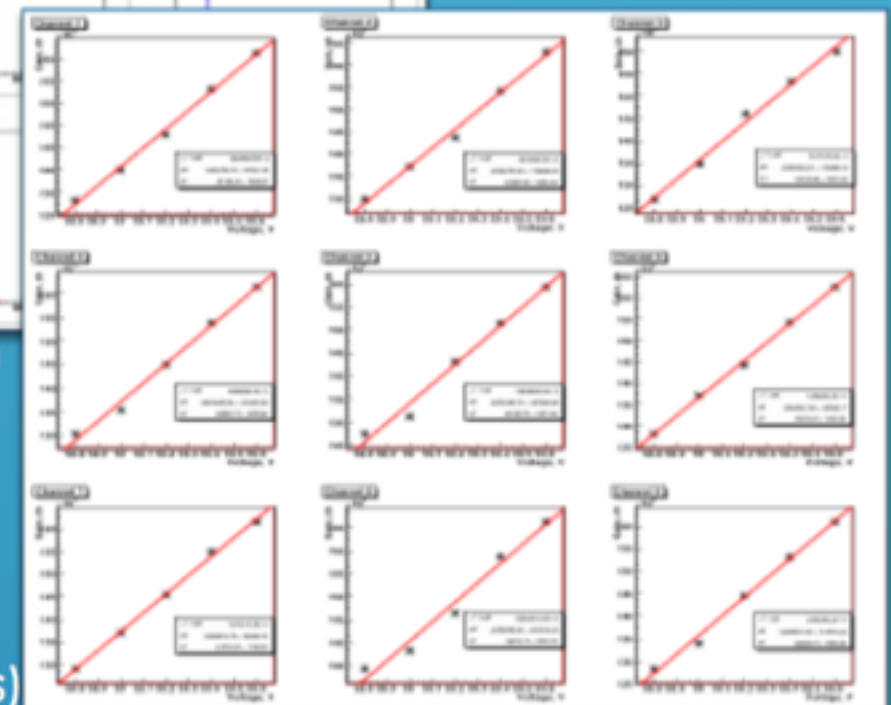


Fig.3.3: Gain vs voltage



# COMPASS (A. Rybnikov)

## 2. Cross-check SiPM operation at low intensity light:

An additional cross-check was performed at low intensity light for operating voltage to get single photoelectron spectra. Then all spectra were analysed as shown on the fig.4.1.

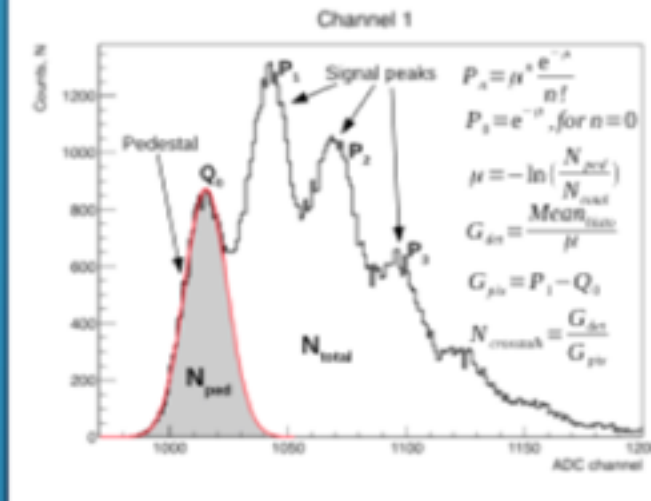


Fig.4.1: Analysis of a charge spectrum with low intensity light

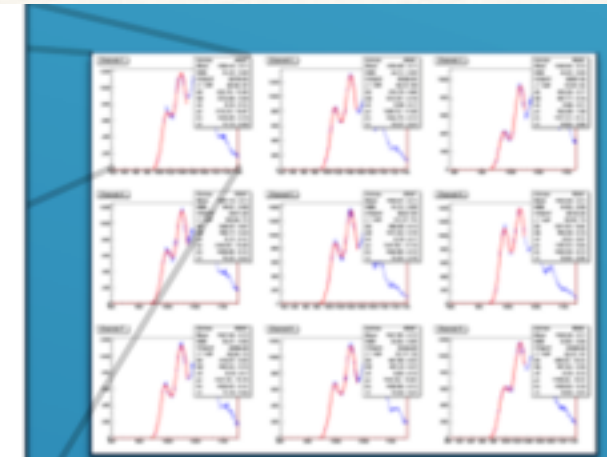


Fig.4.2: Charge spectra at low intensity light

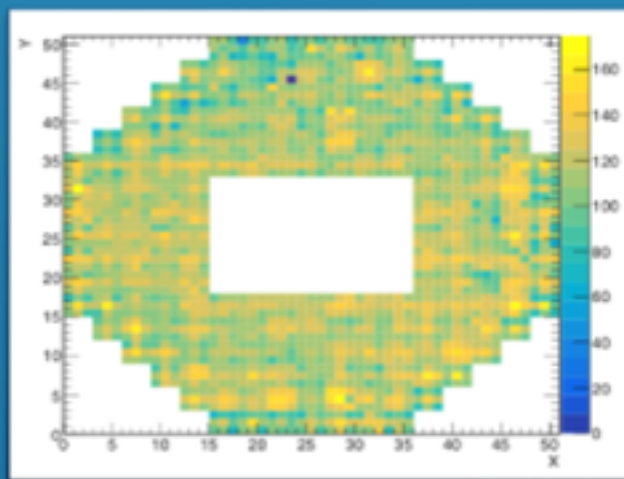


Fig.6.1: ECAL0 amplitude map for muons (COMPASS beam)

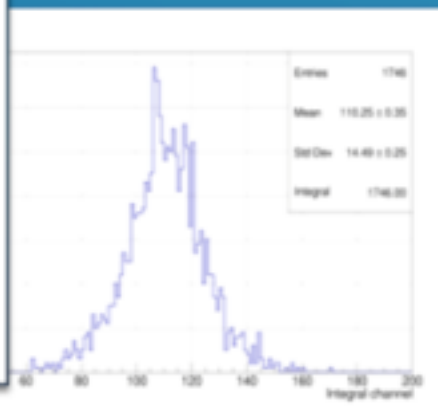


Fig.6.2: ECAL0 amplitude distribution for muons

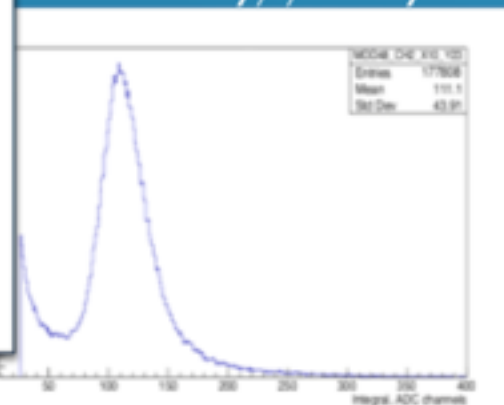


Fig.6.3: Charge spectrum of a single channel for muons

Fig.5: Stand for calibration of calorimetric module using cosmic muons

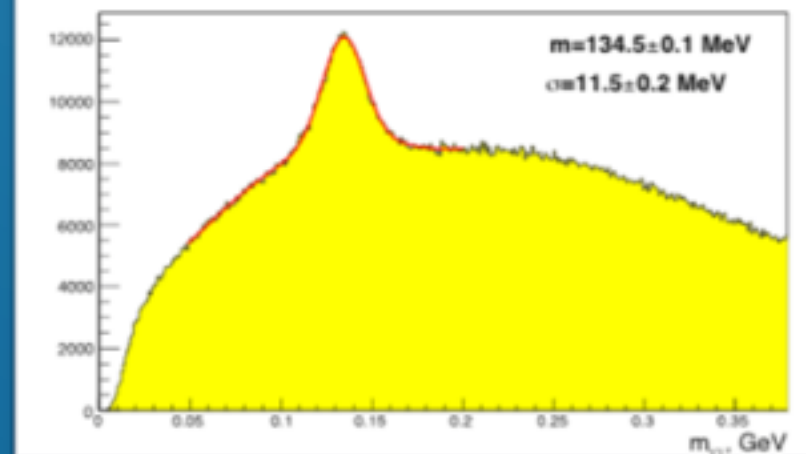


Fig.7: Reconstruction of  $\pi^0$  peak, analyzed by A. Guskov

# ScTil for PANDA (K. Suzuki, W. Nalti)

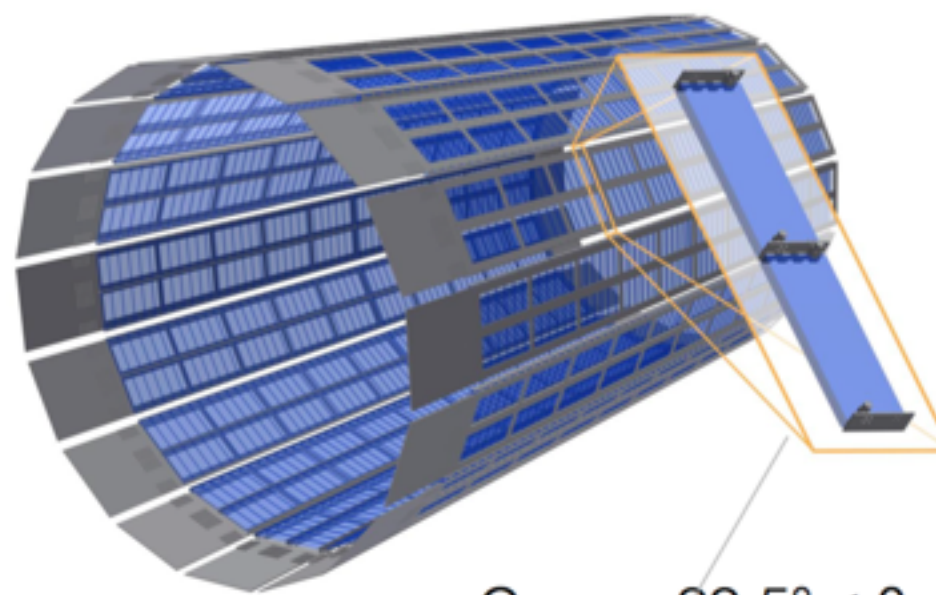
## Barrel Time-of-Flight (TOF) Design

2.46m long, 1m diameter

16 Super modules

240 ch. /SM

max. 40 kHz /ch.



Covers  $22.5^\circ < \theta < 140^\circ$

180x18 cm<sup>2</sup> scintillators (120x) area

2 ch./scint.

rest is left for FEE

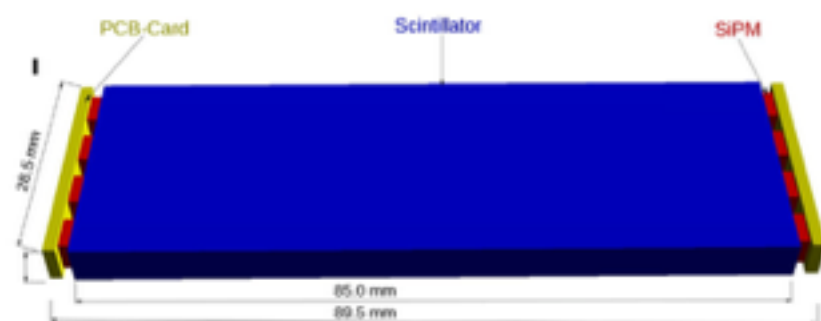
Scintillator Tile

Total: 1920 tiles, 3840 channels, 15360 SiPMs

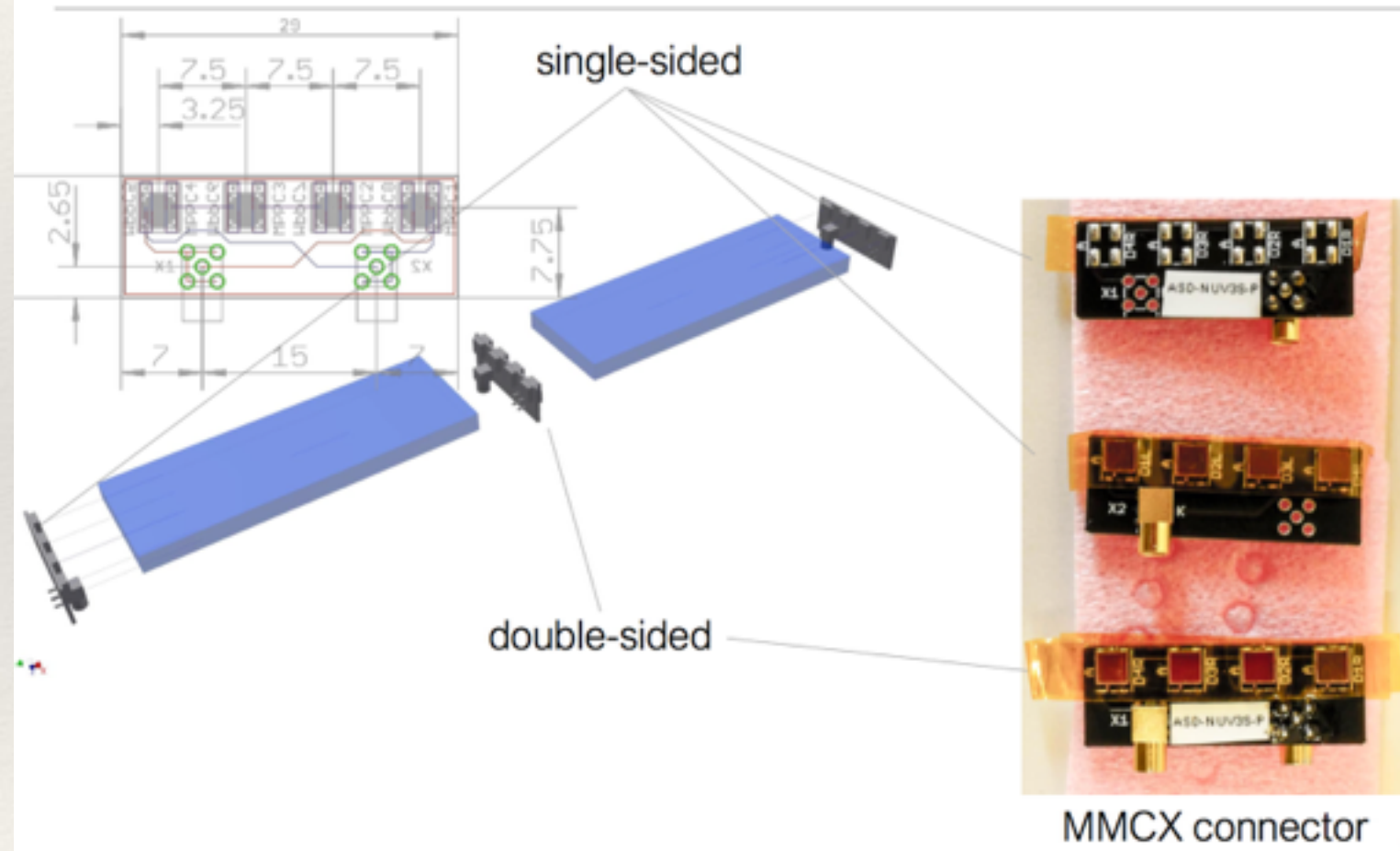


# ScTil for PANDA (K. Suzuki, W. Nalti)

## Single Tile Design



## Dual Module



# ScTil for PANDA (K. Suzuki, W. Nalti)

## Front End Electronics

66cm allocated for FEE  
TOFPET2 ASIC readout



thickness	Npe1	Npe2	time-resolution (ps)
3mm	72.37	46.84	60.34
4mm	85.64	55.14	68.09
5mm	139.94	128.69	50.14
5mm polished	111.87	78.1	48.29
6mm	101.7	70.7	48.7

## Side view of the Sensorboard

Surface coverage = 1/4

scintillator (28.5x5 mm<sup>2</sup>)

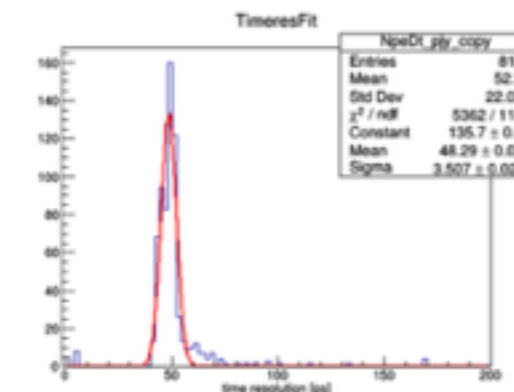
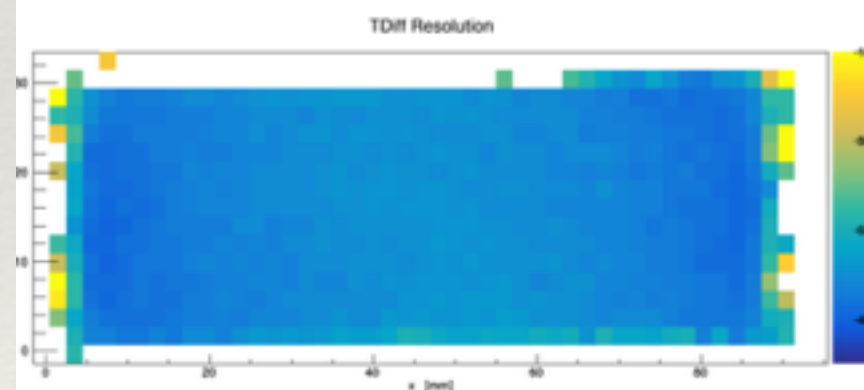
SiPM (3x3 mm<sup>2</sup>)

LED

Temperature sensor



Run 47 / 5 mm polished



less 100 ps  
Time resolution!

Physical performance (TOF),  
no SiPM itself!



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# Issues:

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- ❖ Preparation of the tests: SMD is hard to test, providing homogenous light, etc.
- ❖ IV-curves are good for production and preselection (wafer, casing, batch testing)  
**Restricted number of parameters**
- ❖ High intensity light can be used where single electron resolution hard to provide (limited dynamic range, gain, SPE degradation etc.) **Poissonian distribution!**
- ❖ Low-intensity gives best precision and variety of parameter but **requires special conditions: good SPE, time consumable (statistical precision!), etc**
- ❖ **Need to provide stable environment.**
- ❖ Sampling studying for temperature, spectral, MTTF, radiation hardness etc.
- ❖ Physical calibration SiPM+detector shows final performance.

Thank you for participation!